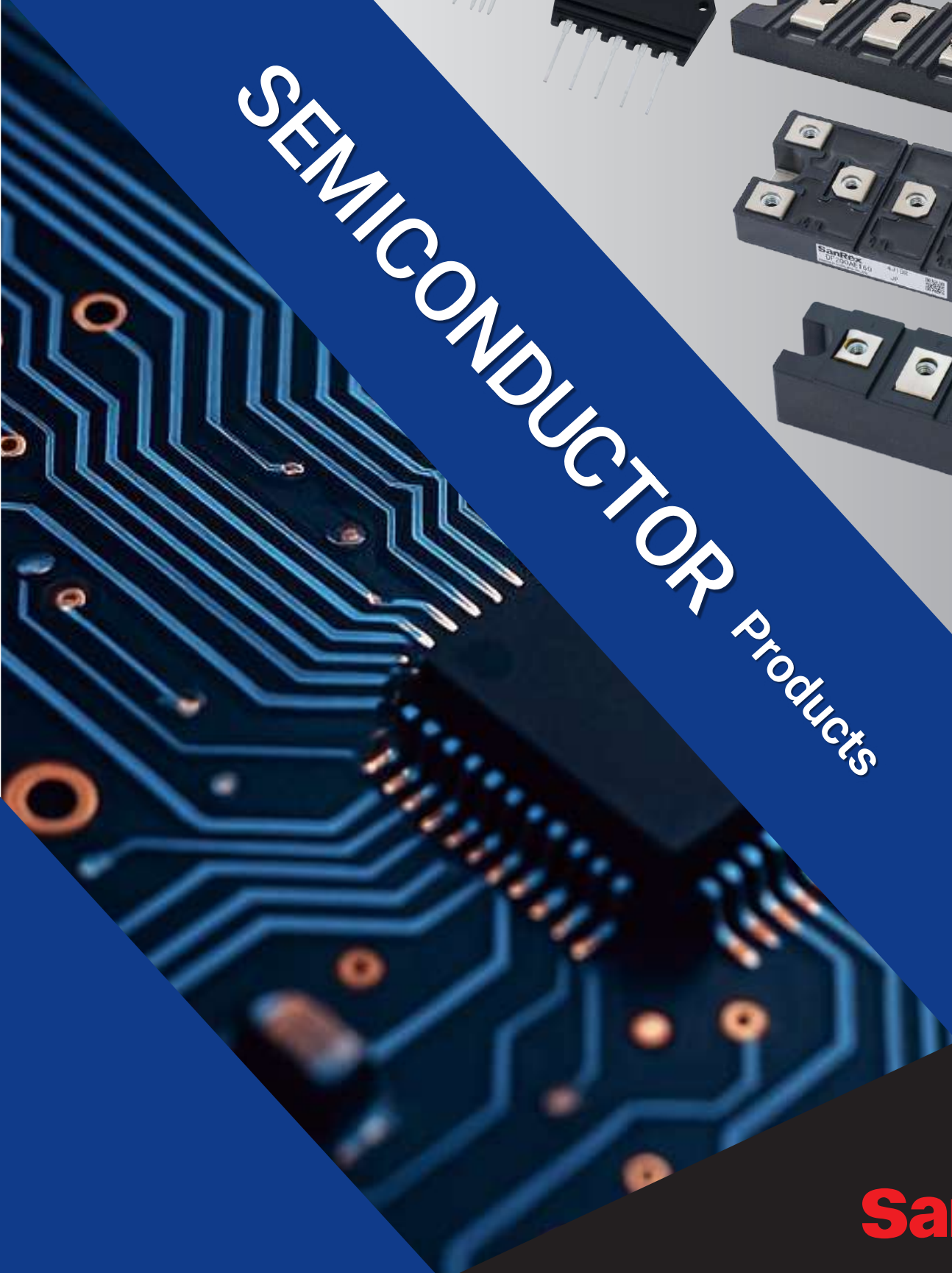
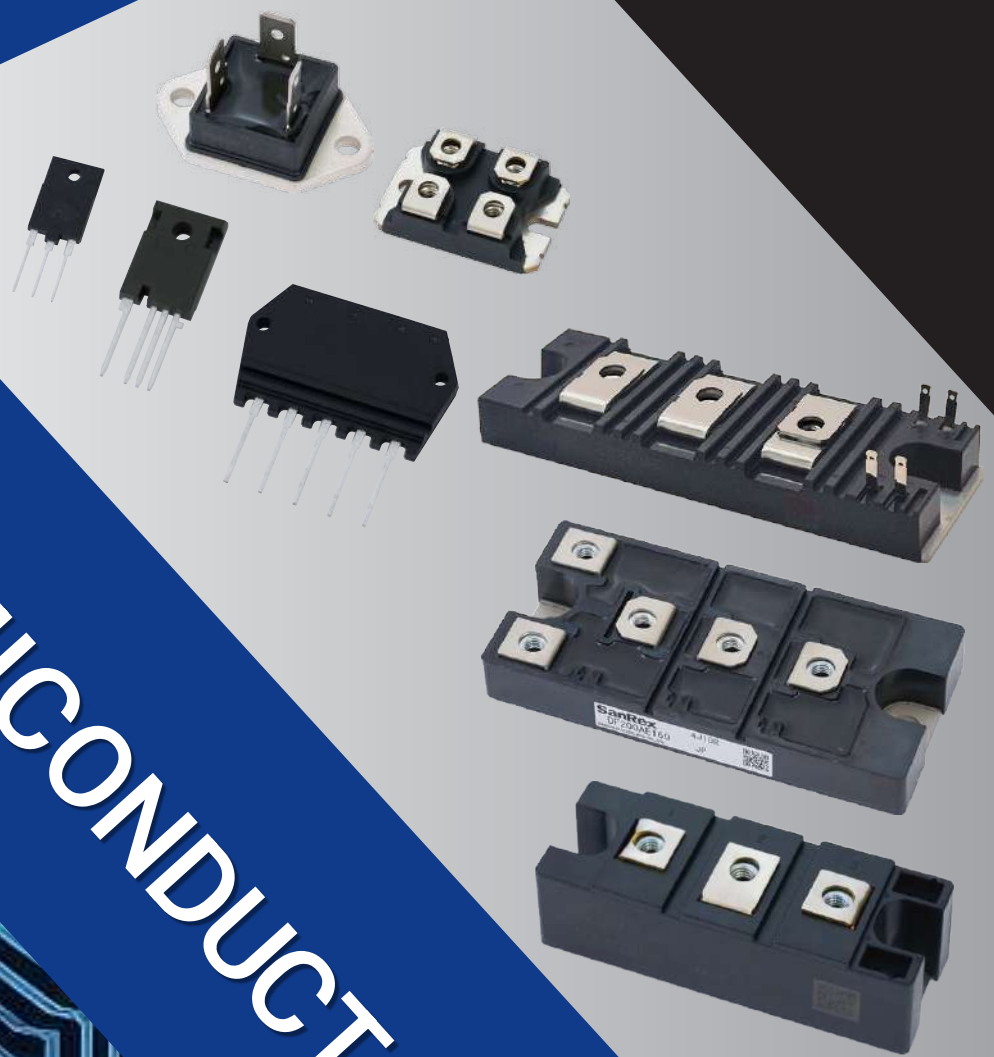


SEMICONDUCTOR Products





◆ SYMBOLS & TERMS	2
◆ SELECTION GUIDE	3

◆ POWER MODULES

• PRODUCT FEATURES	5
• TYPE DESIGNATION	5
• DIODES / FRDs / SBDs	
Fast & Soft Recovery Diodes	6
Fast Recovery Diodes	6
Rectifier Diodes	6
Schottky Barrier Diodes	7
3-Phase Diode Bridge DF-NA/NB Series	7
3-Phase Diode Bridge DF-AC/AE Series	7
3-Phase Diode Bridge DF-AA/BA/CA Series	7
3-Phase Diode Bridge DF-LA/LB Series	7
3-Phase Diode Bridge with Built-in Thyristor	8
3-Phase Half Controlled Rectifier Bridge Modules	8
• THYRISTORS	
High Current Thyristors	8
Thyristor PK/PD Series	8
Thyristor SCA/SCE Series	9
3-Phase Half Controlled Bridge Rectifiers	9
• IGBT/SiC MOSFETs	
IGBT GSA Series	9
SiC MOSFET FCA Series	9
• OUTLINE DRAWINGS	10

◆ DISCRETES

• PRODUCT FEATURES	15
• TYPE DESIGNATION	15
• TRIACS	
Through Hole Standard Gate	16
Through Hole Sensitive Gate	16
Through Hole T _j max=150°C	16
SMD(Surface Mount Device) Standard Gate	17
SMD(Surface Mount Device) Sensitive Gate	17
SMD(Surface Mount Device) T _j max=150°C	17
Tab Terminal Standard Gate	17
• THYRISTORS	
Through Hole Standard Gate	17
Through Hole Sensitive Gate	17
SMD(Surface Mount Device) Standard Gate	17
SMD(Surface Mount Device) Sensitive Gate	18
Tab Terminal Standard Gate	18
• FRDs	
Through Hole	18
Tab Terminal	18
• DIODES	
Through Hole	18
Tab Terminal	18
• SiC MOSFETs	
SiC MOSFET FMG Series	18
• OUTLINE DRAWINGS	19
• PACKAGING SPECIFICATIONS	22



SYMBOLS & TERMS

FRD		DIODE		THYRISTOR		TRIAC	
Symbol	Terminology	Symbol	Terminology	Symbol	Terminology	Symbol	Terminology
V_{ISO}	Dielectric Withstand Voltage	V_{ISO}	Dielectric Withstand Voltage	V_{ISO}	Dielectric Withstand Voltage	V_{ISO}	Dielectric Withstand Voltage
V_{RRM}	Repetitive Peak Reverse Voltage	V_{RRM}	Repetitive Peak Reverse Voltage	V_{DRM}	Repetitive Peak Off-State Voltage	V_{DRM}	Repetitive Peak Off-State Voltage
$I_{F(AV)}$	Average Forward Current	$I_{F(AV)}$	Average Forward Current	V_{RRM}	Repetitive Peak Reverse Voltage	$I_{T(RMS)}$	RMS On-State Current
I_{FSM}	Surge Forward Current	I_D	Output Current (D.C.)	$I_{T(AV)}$	Average On-State Current	I_D	Off-State Current
I^2t	I^2t (for fusing)	I_{FSM}	Surge Forward Current	$I_{T(RMS)}$	RMS On-State Current	V_T	Peak On-State Voltage
V_F	Forward Voltage	I^2t	I^2t (for fusing)	I_{TSM}	Surge On-State Current	I_{GT}	Gate Trigger Current
I_R	Reverse Current	V_F	Forward Voltage	I^2t	I^2t (for fusing)	V_{GT}	Gate Trigger Voltage
trr	Reverse Recovery Time	I_R	Reverse Current	I_{GT}	Gate Trigger Current	T_j	Operating Junction Temperature
T_j	Operating Junction Temperature	T_j	Operating Junction Temperature	V_{GT}	Gate Trigger Voltage	$[dv/dt]_c$	Critical Rate of Rise of Off State Voltage at Commutation
$R_{th(j-c)}$	Thermal Resistance	$R_{th(j-c)}$	Thermal Resistance	I_D	Off-State Current	$R_{th(j-c)}$	Thermal Resistance

IGBT

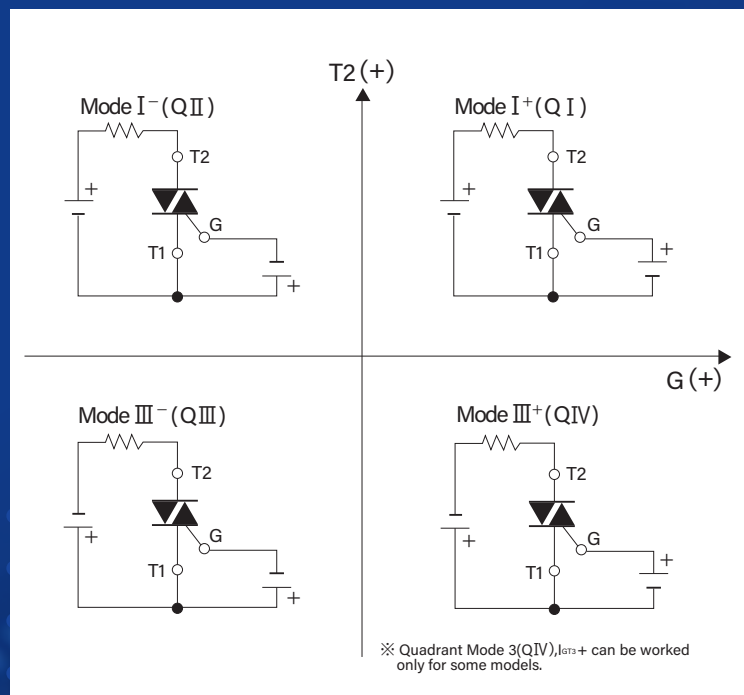
Symbol	Terminology	
V_{ISO}	Dielectric Withstand Voltage	
IGBT	V_{CES}	Collector-Emitter Voltage
	V_{GES}	Gate-Emitter Voltage
	I_C	Collector Current
	$V_{CE(sat)}$	Collector-Emitter Saturation Voltage
	$V_{GE(th)}$	Gate-Source Threshold Voltage
	t_{on}	Turn-On Time : $t_{d(on)} + t_r$
	t_{off}	Turn-Off Time : $t_d(off) + t$
FWD	trr	Reverse Recovery Time

SiC MOSFET

Symbol	Terminology	
V_{ISO}	Dielectric Withstand Voltage	
MOSFET	V_{DSS}	Drain-Source Breakdown Voltage
	I_D	Continuous Drain-Source Current
	V_{GSS}	Gate-Source Voltage
	$R_{DS(on)}$	Drain-Source On-State Resistance
	$V_{GS(th)}$	Gate Threshold Voltage
Channel Diode	I_S	Continuous Diode Forward Current
	V_{SD}	Diode Forward Voltage
$R_{th(j-c)}$	Thermal Resistance	

I_R	Reverse Current
dv/dt	Critical Rate of Rise of Off-State Voltage
di/dt	Critical Rate of Rise of On-State Current
T_j	Operating Junction Temperature
$R_{th(j-c)}$	Thermal Resistance

◆ GATE TRIGGER MODE for TRIACS (Quadrant definitions)





SELECTION GUIDE

Converter Bridge

DFA series
800~1600V
50~200A
P.8 ▶▶

DF series
800~1600V
20~200A
P.7 ▶▶

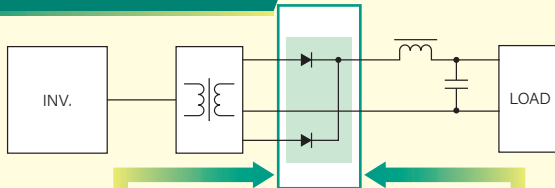
DCA series
800~2200V
200/240A
DD series
800~1600V
60~300A
P.6 ▶▶

PD SCE series
800~1800V
25~250A
P.8,9 ▶▶

PK SCA series
800~1800V
25~250A
P.8,9 ▶▶

SFF series
800V
200A
P.8 ▶▶

Secondary Rectifier



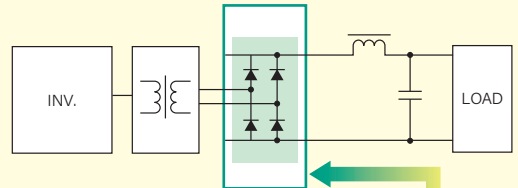
DBA series
400/600V
200A
Fast Recovery Diodes
P.6 ▶▶

FRS FRG DSR DMG series
500~2000V
25~400A
Fast Recovery Diodes
P.6,18 ▶▶

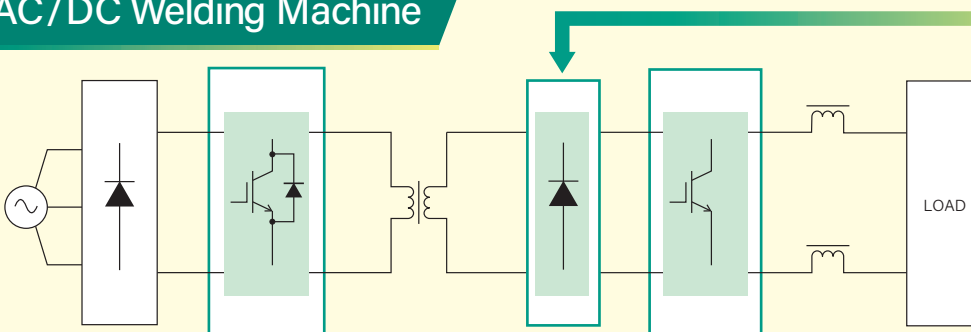
DKA FRD DKR series
600~3000V
40~400A
Fast Recovery Diodes
BKR series
50/100V
400A
Schottky Barrier Diodes
P.6,7 ▶▶

DCA FDS series
600~1200V
100~200A
Fast Recovery Diodes
P.6 ▶▶

FDF series
600/1200V
25/60A
Fast Recovery Diodes
P.6 ▶▶



AC/DC Welding Machine



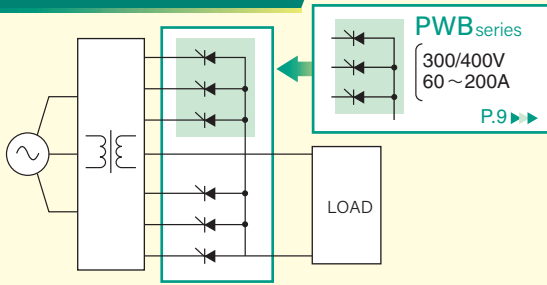
GSA series
1200V
75A
IGBT
P.9 ▶▶

GSA series
600V
100A
IGBT
P.9 ▶▶

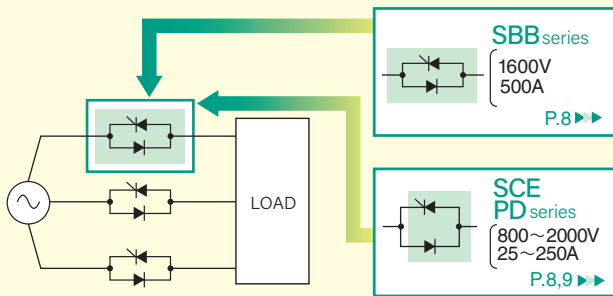
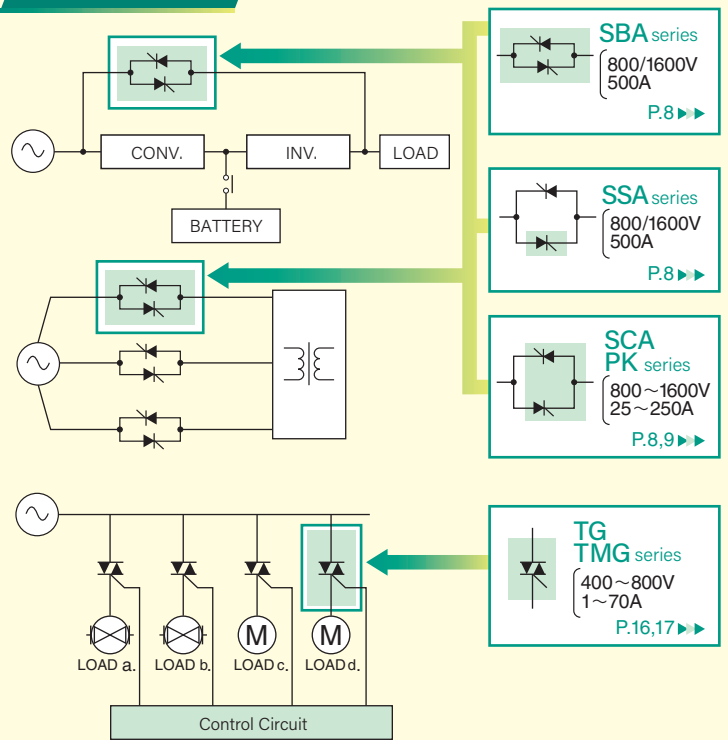
DBA series
400/600V
200A
Fast Recovery Diodes
P.6 ▶▶



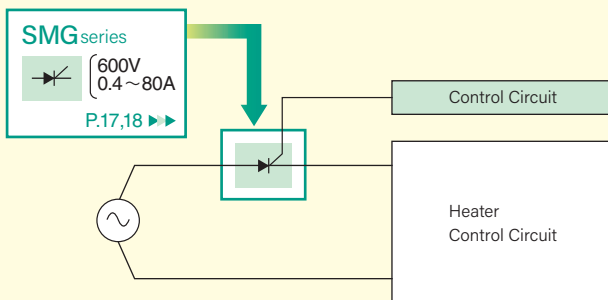
3-Phase Control



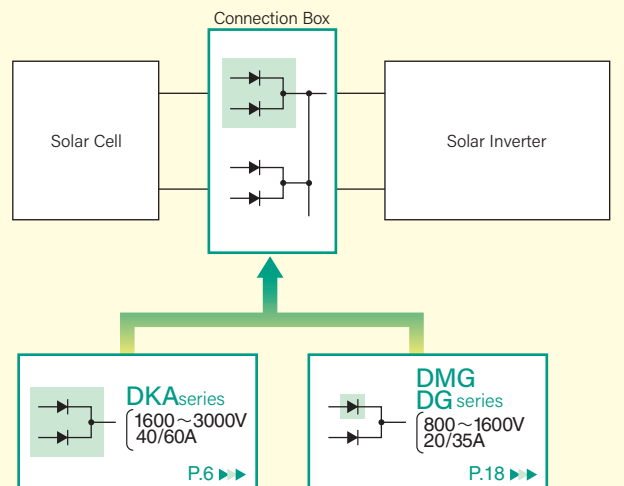
AC Control



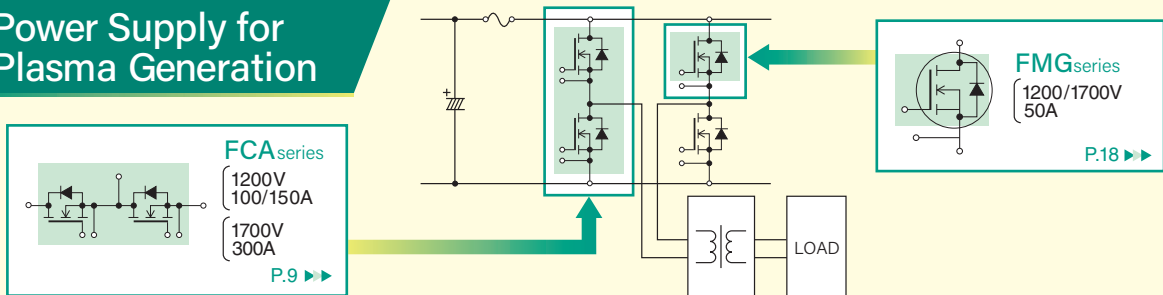
Heating System



Solar(PV)Power Generation System



Power Supply for Plasma Generation



POWER MODULES



PRODUCT FEATURES

Fast Recovery Diodes

In addition to Fast Recovery Diodes designed to minimize switching losses, Soft Recovery Diodes which have advantages of very low noises are additionally developed and demonstrates energy-saving effects.

< Soft Recovery Series >

- DCA series** Two types of Reverse Recovery Times
- DBA series** Two types of Reverse Recovery Times with Soft Recovery Characteristics
- DKA series** Common cathode type

< Fast Recovery Series >

- FD series** Single phase FRD bridge
- FRS series** High current diodes up to 400A
- DBA series** High speed type
- DKR series** Compact non-isolated package, dual diodes with common cathode
- FRD FDS series** Dual diode modules

Diodes / Thyristor rectifiers

The lineup includes diodes rated up to 3000V and thyristors rated up to 2200V. with high dv/dt, surge current capabilities designed for up to 690VAC input . 3-phase bridge diode modules: Available variety of packages in height achieving easy connecting and compact design.

- DF series** Various configurations for 3-phase bridge diodes
 - DF_AA/BA : Standard models
 - DF_CA : High surge current capability models
 - DF_NA/NB : Compact SIP (=Single-In-line Package) /DIP (=Dual-In-line Package) modules
 - DF_AC/AE : 17mm low profile modules
 - DF_LA/LB : Available two types of designs on package:
 - LB type: With barrier for keeping creepage distance between terminals
 - LA type: Without barrier for easy connection with other devices

- DFA series** 3-phase bridge diode with built-in thyristor for preventing inrush current for connecting other devices
- DDKDDKA series** Standard dual diode modules, in series (DD), and common cathode (KD)
- BKA BKR series** Schottky Barrier Diodes
- SFF series** 3-Phase Half Controlled Rectifier Bridge Modules
- PK/SCA PD/SCE series** Standard Dual Thyristor and Thyristor/Diode Modules
- PWB series** Standard 3-Phase Half Bridge Thyristor Module

IGBTs

Available two types of models, high-speed and low conduction loss (Low VCE(sat)).

GSA series

SiCs

Achieved very high reliability and ideal switching performance designed by diode current through channel diode

FCA series SiC MOSFET Modules (Half Bridge)

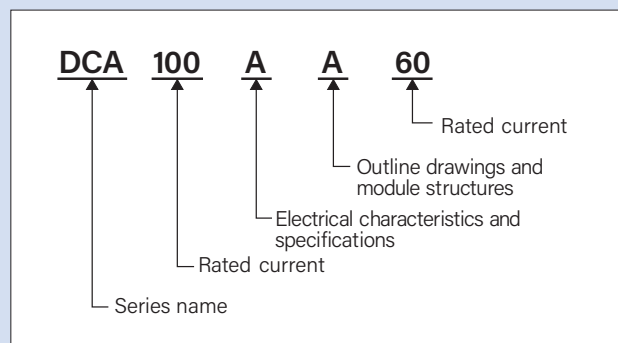
RoHS Compliance

All products shown in catalog are RoHS compliant.

UL Standard Compliant

All products shown in catalogue are UL1557 Standard Compliant (UL File No. E760102) except for models with "Non Isolated Type", "DKA40AA220" and "DKA40BA300"

TYPE DESIGNATION





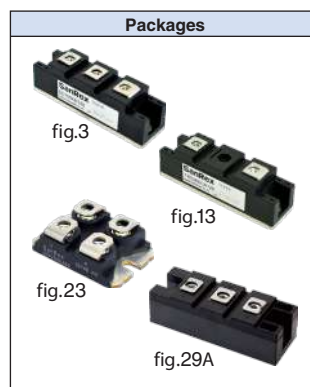
DIODES / FRDs / SBDs

Fast & Soft Recovery Diodes

$V_{iso} : 2500V_{(RMS)}$ $T_{j(max)} : 150^{\circ}C$

Type	V_{RRM} V	$I_{F(AV)}$		I_{FSM} A(60Hz)	I^2t A ² s	V_{FM} V(25°C)	I_{RRM} mA(125°C)	t_{rr} ns	R_{thj-c} °C/W	Fig No.
		A	°C							
DCA100AA60	600	100	85	2000	16700	1.3	100	300	0.5	3
DCA150AA60	600	150	72	2500	26000	1.3	150	300	0.4	3
DCA100BA60	600	100	80	1350	7500	1.55	100	200	0.45	3
DCA150BA65	650	150	63	1500	9300	1.7	150	200	0.34	3
DCA200UA65	650	200	85	1350	7500	1.7	50(150°C)	360	0.19	29A
DKA200AA60	600	100	85	2000	16700	1.3	100	300	0.5	3
DKA300AA60	600	150	72	2500	26000	1.3	150	300	0.4	3
DSR200BA60	600	200	85	3300	45000	1.3	200	300	0.25	13
DBA200UA40	400	100	96	700	2100	1.2	100(150°C)	130	0.45	23
DBA200UA60	600	100	89	700	2100	1.35	100(150°C)	250	0.45	23
DBA200WA40	400	100	96	1100	5050	1.2	4	110	0.45	23
DBA200WA60	600	100	89	1100	5050	1.5	4	130	0.45	23

Connections



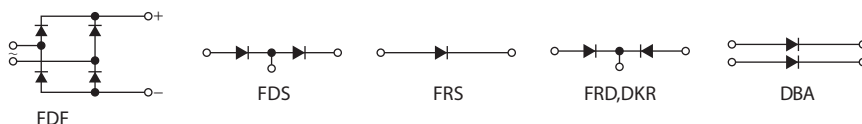
Fast Recovery Diodes

$V_{iso} : 2500V_{(RMS)}$ $T_{j(max)} : 150^{\circ}C$

Type	V_{RRM} V	$I_{F(AV)}$		I_{FSM} A(60Hz)	I^2t A ² s	V_{FM} V(25°C)	I_{RRM} mA(125°C)	t_{rr} ns	R_{thj-c} °C/W	Fig No.
		A	°C							
FDf25CA120	1200	25	114	400	660	1.8	2(150°C)	200	0.4	6
FDf60BA60	600	60	80	600	1490	1.6	60	100	0.36	6
FRD100CA120	1200	100	78	2000	16600	1.8	5(150°C)	300	0.4	3
FDS100CA120	1200	100	78	2000	16600	1.8	5(150°C)	300	0.4	3
FRS150BA50	500	150	85	3000	37500	1.3	150	200	0.33	7
FRS200CA120	1200	200	78	3300	45000	1.8	10(150°C)	350	0.2	13
FRS300BA50/60	500, 600	300	85	4000	66600	1.3	300	200	0.165	7
FRS400BA60	600	400	94	4000	66640	1.4	400	200	0.1	8
FRS400CA120	1200	400	78	4000	66640	1.8	20(150°C)	400	0.1	8
FRS400EA200	2000	400	79	5000	104000	2.2(125°C)	100(150°C)	700	0.08	8
DKR400CA60*	600	200	105	5600	130000	1.6	100	200	0.14	37
DBA200YA40	400	100	89	1100	5000	1.35	6(150°C)	85	0.45	23

*Non isolated type

Connections



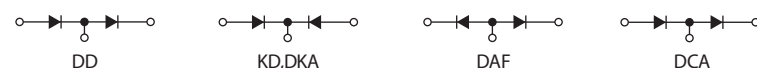
Rectifier Diodes

$V_{iso} : 2500V_{(RMS)}$ $T_{j(max)} : 150^{\circ}C$

Type	V_{RRM} V	$I_{F(AV)}$		I_{FSM} A(60Hz)	I^2t A ² s	V_{FM} V(25°C)	I_{RRM} mA(125°C)	R_{thj-c} °C/W	Fig No.
		A	°C						
DKA40AA220	2200	20	125	1080	4860	1.15	10	0.65	31
DKA40BA300	3000	20	125	910	3440	1.15	10	0.09	38
DD60KB80/160	800, 1600	60	110	1200	6000	1.35	20	0.52	3
KD60GB80	800	60	114	1200	6000	1.25	20	0.5	3
KD60HB160	1600	60	111	1200	6000	1.35	20	0.5	3
DKA60KB80/160	800, 1600	60	110	1200	6000	1.35	20	0.52	3
DD100KB80/160	800, 1600	100	105	2000	16500	1.35	30	0.35	3
DD160KB80/160	800, 1600	160	90	3200	42600	1.35	30	0.3	3
KD160KB80/160	800, 1600	160	90	3200	42600	1.35	30	0.3	3
DAF160AA40*	400	160	90	3200	42600	1.3	30	0.29	35
DCA200DB80/160	800, 1600	200	113	5500	125000	1.3	50	0.15	29C
DCA200DB220	2200	200	113	5500	125000	1.4	50	0.15	29C
DCA240DB80/160	800, 1600	240	110	5500	125000	1.35	50	0.15	29C
DCA240EB80/160	800, 1600	240	110	5500	125000	1.35	50	0.12	29C
DD300KB80/160	800, 1600	300	91	6000	150000	1.5	50	0.14	4

*Non isolated type

Connections

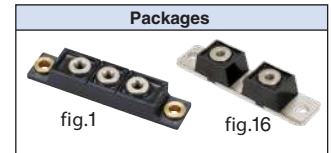
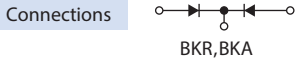


Schottky Barrier Diodes

$V_{iso} : 2500V_{(RMS)}$ $T_{j(max)} : 150^{\circ}C$

Type	V_{RRM} V	$I_{F(AV)}$		I_{FSM} A(60Hz)	I^2t A ² s	V_{FM} V(25°C)	I_{RRM} mA(125°C)	Rthj-c °C/W	Fig No.
		A	°C						
BKR400ABZ50*	50	200	127	7600	240000	0.57	2000	0.2	16
BKR400AB10*	100	200	112	3620	54450	0.82	40	0.2	16
BKA400AB10	100	200	83	3620	54450	0.82	140	0.4	1

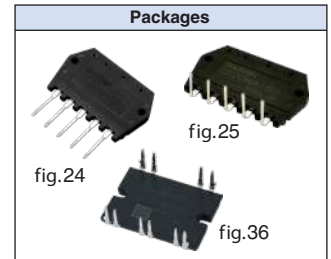
*Non isolated type



3-Phase Diode Bridge DF-NA/NB Series

$V_{iso} : 2500V_{(RMS)}$ $T_{j(max)} : 150^{\circ}C$

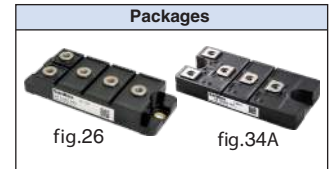
Type	V_{RRM} V	I_D		I_{FSM} A(60Hz)	I^2t A ² s	V_{FM} V(25°C)	I_R mA(150°C)	Rthj-c °C/W	Fig No.
		A	°C						
DF20NA80/160S	800, 1600	20	111	350	500	1.2	4/8	0.8	24
DF20NA80/160F1	800, 1600	20	111	350	500	1.2	4/8	0.8	25
DF30NA80/160S	800, 1600	30	92	400	660	1.2	5/14	0.8	24
DF30NA80/160F1	800, 1600	30	92	400	660	1.2	5/14	0.8	25
DF60NB160	1600	60	110	800	2600	1.3	8	0.25	36
DF75NB160	1600	75	112	1000	4100	1.3	8	0.2	36
DF100NB160	1600	100	98	1000	4100	1.35	8	0.2	36



3-Phase Diode Bridge DF-AC/AE Series

$V_{iso} : 2500V_{(RMS)}$ $T_{j(max)} : 150^{\circ}C$

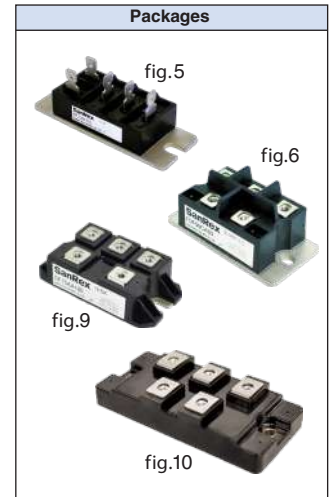
Type	V_{RRM} V	I_D		I_{FSM} A(60Hz)	I^2t A ² s	V_{FM} V(25°C)	I_R mA(150°C)	Rthj-c °C/W	Fig No.
		A	°C						
DF75AC80/160	800, 1600	75	100	1000	4100	1.4	10	0.24	26
DF100AC80/160	800, 1600	100	102	1300	7000	1.2	15	0.2	26
DF150AE80/160	800, 1600	150	106	2000	17000	1.31	15	0.11	34A
DF200AE80/160	800, 1600	200	106	2500	26000	1.32	20	0.08	34A



3-Phase Diode Bridge DF-AA/BA/CA Series

$V_{iso} : 2500V_{(RMS)}$ $T_{j(max)} : 150^{\circ}C$

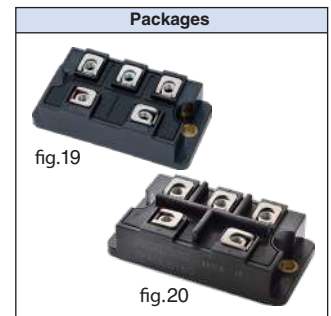
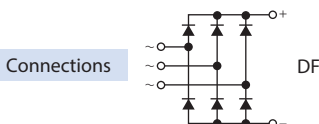
Type	V_{RRM} V	I_D		I_{FSM} A(60Hz)	V_F V(25°C)	I_R mA(150°C)	Rthj-c °C/W	Fig No.
		A	°C					
DF20CA80/160	800, 1600	20	123	600	1.1	8	0.6	5
DF20AA120/160	1200, 1600	20	119	240	1.25	3	0.6	5
DF30CA80/160	800, 1600	30	122	850	1.1	12	0.42	5
DF30AA120/160	1200, 1600	30	117	300	1.3	3	0.42	5
DF40BA80	800	40	119	700	1.2	4	0.32	6
DF40AA120/160	1200, 1600	40	116	700	1.3	3	0.32	6
DF50BA80	800	50	114	700	1.2	4	0.3	9
DF50AA120/160	1200, 1600	50	114	700	1.2	8	0.3	9
DF60BA80	800	60	115	1000	1.2	6	0.24	6
DF60AA120/160	1200, 1600	60	112	1000	1.3	12	0.24	6
DF75BA80	800	75	107	1000	1.2	10	0.24	9
DF75AA120/160	1200, 1600	75	100	1000	1.4	10	0.24	9
DF100BA80	800	100	102	1000	1.2	15	0.2	9
DF100AA120/160	1200, 1600	100	102	1000	1.2	15	0.2	9
DF150AB80/160	800, 1600	150	100	1200	1.2	15	0.14	10
DF200AB80/160	1200, 1600	200	102	2000	1.2	20	0.1	10



3-Phase Diode Bridge DF-LA/LB Series

$V_{iso} : 2500V_{(RMS)}$ $T_{j(max)} : 150^{\circ}C$

Type	V_{RRM} V	I_D		I_{FSM} A(60Hz)	V_F V(25°C)	I_R mA(150°C)	Rthj-c °C/W	Fig No.
		A	°C					
DF60LA80/160	800, 1600	60	111	800	1.3	8	0.25	19
DF60LB80/160	800, 1600	60	111	800	1.3	8	0.25	20
DF75LA80/160	800, 1600	75	101	1000	1.3	8	0.25	19
DF75LB80/160	800, 1600	75	101	1000	1.3	8	0.25	20
DF100LA80/160	800, 1600	100	90	1300	1.3	12	0.23	19
DF100LB80/160	800, 1600	100	90	1300	1.3	12	0.23	20

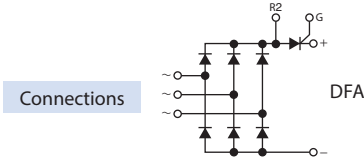




3-Phase Diode Bridge with Built-in Thyristor

V_{iso} : 2500V(RMS)

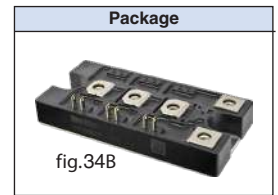
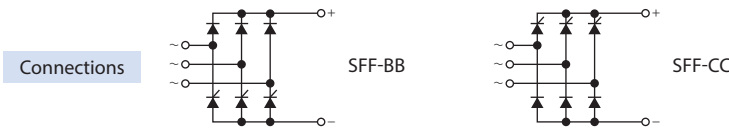
Type	V _{DRM} /V _{RRM} V	I _D		I _{FSM} A(60Hz)	I ² t A ² s	V _{FM(D)} V(25°C)	I _{RRM(D)} mA(150°C)	R _{thj-c(D)} °C/W	V _{TM(THY)} V(25°C)	I _{RRM(THY)} mA(135°C)	R _{thj-c(THY)} °C/W	T _{j(max)}		Fig No.
		A	°C									(thy)	(Diode)	
DFA50BA80/160	800, 1600	50	117	800	2660	1.3	8	0.25	1.25	50	0.8	135°C	150°C	15
DFA75BA80/160	800, 1600	75	101	1000	4150	1.3	8	0.25	1.2	60	0.4	135°C	150°C	15
DFA100BA80/160	800, 1600	100	98	1300	7030	1.3	12	0.2	1.2	70	0.36	135°C	150°C	15
DFA150BA80/160	800, 1600	150	105	1600	10670	1.35	15	0.09	1.35	100	0.22	150°C	150°C	15
DFA150AA80/160	800, 1600	150	93	1600	10670	1.35	15	0.14	1.35	100	0.21	135°C	150°C	28
DFA200AA80/160	800, 1600	200	96	2000	17000	1.35	20	0.1	1.15	50	0.18	135°C	150°C	28
DFA250AA80/160	800, 1600	250	96	2000	17000	1.4	20	0.077	1.25	100	0.132	135°C	150°C	28
DFA150CB80/160	800, 1600	150	113	1600	10670	1.35	15	0.09	1.35	100	0.18	150°C	150°C	17
DFA200CB80/160	800, 1600	200	96	2000	17000	1.35	20	0.1	1.15	50	0.15	150°C	150°C	17



Thyristor/Diode 3-Phase Bridge (Half Control)

V_{iso} : 2500V(RMS) dv/dt : 500V/μs T_{j(max)} : 125°C

Type	V _{DRM} /V _{RRM} V	I _D		I _{TSM} A(60Hz)	I ² t A ² s	I _{GT} mA(25°C)	V _{GT} V(25°C)	V _T V(25°C)	I _D /I _R mA	R _{thj-c} °C/W	T _{j(max)} °C	Fig No.
		A	°C									
SFF200BB80	800	200	92	2300	22000	150	3	1.35	15	0.06	125	34B
SFF200CC80	800	200	92	2300	22000	150	3	1.35	15	0.06	125	34B

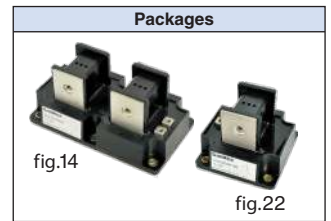
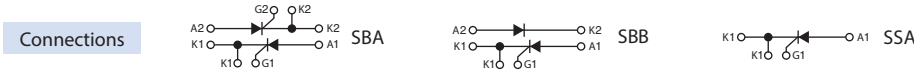


THYRISTORS

High Current Thyristors

V_{iso} : 2500V(RMS) dv/dt : 500V/μs T_{j(max)} : 125°C

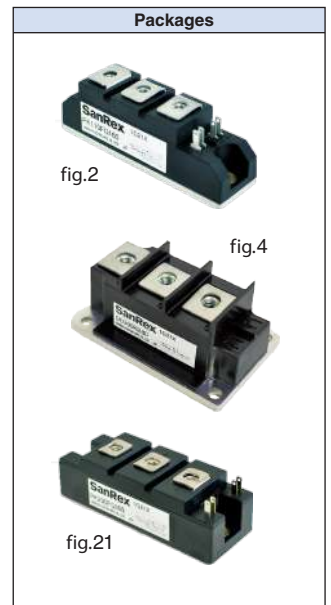
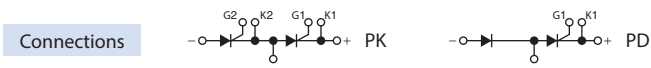
Type	V _{DRM} /V _{RRM} V	I _{T(AV)}		I _{TSM} A(60Hz)	I ² t A ² s	I _{GT} mA(25°C)	V _{GT} V(25°C)	V _{TM} V(25°C)	I _{DRM} /I _{RRM} mA(125°C)	R _{thj-c} °C/W	Fig No.
		A	°C								
SBA500AA80/160	800, 1600	500	66	10000	4.16×10 ⁵	200	3	1.45	150	0.085	14
SBB500AA160	1600	500	66	10000	4.16×10 ⁵	200	3	1.45	150	0.085	14
SSA500AA80/160	800, 1600	500	66	10000	4.16×10 ⁵	200	3	1.45	150	0.085	22



Thyristor PK/PD Series

V_{iso} : 2500V(RMS) dv/dt : 500V/μs T_{j(max)} : 125°C

Type	V _{DRM} /V _{RRM} V	I _{T(AV)}		I _{TSM} A(60Hz)	I ² t A ² s	I _{GT} mA(25°C)	V _{GT} V(25°C)	V _{TM} V(25°C)	I _{DRM} /I _{RRM} mA(125°C)	R _{thj-c} °C/W	Fig No.
		A	°C								
PK25FG80/160	800, 1600	25	81	700	2870	50	3	1.6	5	1.1	2
PD25FG80/160	800, 1600	25	81	700	2870	50	3	1.6	5	1.1	2
PK40FG80/160	800, 1600	40	83	950	3760	50	3	1.6	10	0.65	2
PD40FG80/160	800, 1600	40	83	950	3760	50	3	1.6	10	0.65	2
PK55FG80/160	800, 1600	55	81	1300	7040	50	3	1.6	15	0.5	2
PD55FG80/160	800, 1600	55	81	1300	7040	50	3	1.6	15	0.5	2
PK70FG80/160	800, 1600	70	84	1600	10660	50	3	1.6	20	0.37	2
PD70FG80/160	800, 1600	70	84	1600	10660	50	3	1.6	20	0.37	2
PK90FG80/160	800, 1600	90	82	2300	22040	50	3	1.6	25	0.3	2
PD90FG80/160	800, 1600	90	82	2300	22040	50	3	1.6	25	0.3	2
PK110FG80/160	800, 1600	110	81	3000	37500	50	3	1.6	30	0.25	2
PD110FG80/160	800, 1600	110	81	3000	37500	50	3	1.6	30	0.25	2
PK130FG80/160	800, 1600	130	83	3500	51040	50	3	1.6	35	0.2	2
PD130FG80/160	800, 1600	130	83	3500	51040	50	3	1.6	35	0.2	2
PK160FG80/160	800, 1600	160	84	5400	125000	100	3	1.5	100	0.18	21
PD160FG80/160	800, 1600	160	84	5400	125000	100	3	1.5	100	0.18	21
PK200FG80/160	800, 1600	200	73	6500	180000	100	3	1.5	100	0.167	21
PD200FG80/160	800, 1600	200	73	6500	180000	100	3	1.5	100	0.167	21
PK250GB80/HB160	800, 1600	250	72	5500	125000	100	3	1.6	50	0.14	4
PD250GB80/HB160	800, 1600	250	72	5500	125000	100	3	1.6	50	0.14	4



Thyristor SCA/SCE Series

$V_{iso} : 2500V/3000V_{(RMS)}$ $dv/dt : 1000V/\mu s$

Type	V_{DRM}/V_{RRM} V	$I_{T(AV)}$		I_{TSM} A(60Hz)	I_{T}^2t A ² s	I_{GT} mA(25°C)	V_{GT} V(25°C)	V_{TM} V(25°C)	I_{DRM}/I_{RRM} mA	R_{thj-c} °C/W	$T_{j(max)}$ °C	Fig No.
		A	°C									
SCA55AA160	1600	55	95	1500	9380	100	2.5	1.65	20(130°C)	0.4	130	30
SCE55AA160	1600	55	95	1500	9380	100	2.5	1.65	20(130°C)	0.4	130	30
SCA70AA160	1600	70	101	1750	12800	100	2.5	1.7	20(130°C)	0.25	130	30
SCE70AA160	1600	70	101	1750	12800	100	2.5	1.7	20(130°C)	0.25	130	30
SCA90AA160	1600	90	100	2300	22040	100	2.5	1.7	20(130°C)	0.2	130	30
SCE90AA160	1600	90	100	2300	22040	100	2.5	1.7	20(130°C)	0.2	130	30
SCA110AA160	1600	110	95	2500	25000	100	2.5	1.7	20(130°C)	0.19	130	30
SCE110AA160	1600	110	95	2500	25000	100	2.5	1.7	20(130°C)	0.19	130	30
SCA160DB80/160	800, 1600	160	88	5900	145000	100	3	1.4	100(125°C)	0.17	125	29C
SCE160CA220	2200	160	85	4500	84000	100	3	1.65	40(130°C)	0.17	130	29B
SCE160DB80/160	800, 1600	160	88	5900	145000	100	3	1.4	100(125°C)	0.17	125	29C
SCA200DB80/160	800, 1600	200	83	6500	180000	100	3	1.34	100(125°C)	0.155	125	29C
SCE200CA220	2200	200	76	5500	125000	100	3	1.7	50(130°C)	0.155	130	29B
SCE200DB80/160	800, 1600	200	83	6500	180000	100	3	1.34	100(125°C)	0.155	125	29C
SCA240DA160	1600	240	86	6500	180000	100	3	1.5	100(125°C)	0.105	125	29B
SCE240DA160	1600	240	86	6500	180000	100	3	1.5	100(125°C)	0.105	125	29B



Connections

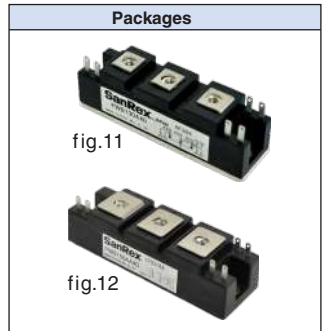
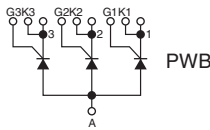


Standard 3-phase thyristor module (Half Bridge)

*Non isolated type
 $di/dt : 50A/\mu s$ $V_{GT} : 2V_{(25°C)}$ $T_{j(max)} : 150°C$

Type	V_{DRM}/V_{RRM} V	$I_{T(AV)}$		$I_{T(RMS)}$		I_{TSM} A(60Hz)	I_{T}^2t A ² s	dv/dt V/ $\mu s(150°C)$	I_{GT} mA(25°C)	V_{TM} V(25°C)	I_{DRM}/I_{RRM} mA(150°C)	R_{thj-c} °C/W	Fig No.
		A	°C	A	°C								
PWB60A30/40	300, 400	60	123	94	123	1800	13500	50	150	1.25	10	0.35	11
PWB80A30/40	300, 400	80	116	125	116	2500	26000	50	150	1.2	12	0.35	11
PWB100A30/40	300, 400	100	114	157	114	3500	51000	50	150	1.2	15	0.3	11
PWB130A30/40	300, 400	130	120	204	112	3500	51000	50	150	1.2	30	0.2	11
PWB150AA30/40	300, 400	150	121	230	121	3500	51000	200	100	1.2	40	0.15	12
PWB200AA40	400	200	121	314	121	6000	149940	200	150	1.2	60	0.12	12

Connections



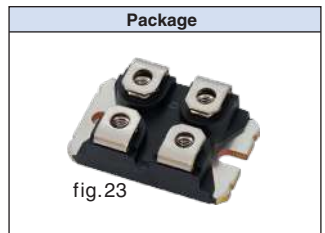
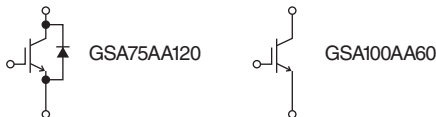
IGBT / SiC MOSFETs

IGBT GSA Series

$V_{iso} : 2500V_{(RMS)}$ $T_{j(max)} : 150°C$

Type	V_{CES} V	V_{GES} V	I_c		IGBT			FWD trr ns	R_{thj-c} °C/W	Fig No.	
			A	°C	$V_{CE(sat)}$ V	$V_{GS(th)}$ V	t_{on} ns				t_{off} ns
GSA75AA120	1200	± 20	75	57	3.90	6.3	115	275	125	0.25(IGBT)	23
GSA100AA60	600	± 20	100	113	1.50	6.7	1260	8780	-	0.25	23

Connections

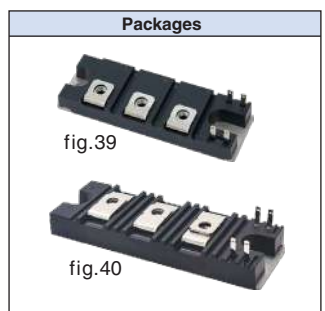
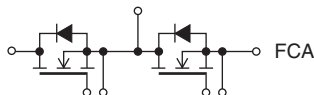


SiC MOSFET FCA Series

$V_{iso} : 4000V_{(RMS)}$ @1700V, 2500V_(RMS)@1200V $T_{j(max)} : 150°C$

Type	V_{bss} V	I_D		V_{GSS} V	$R_{DS(on)}$ m Ω	$V_{GS(th)}$ V	Channel Diode		R_{thj-c} °C/W	Fig No.	
		A	°C				I_D	V_{SD} V			
FCA100AC120	1200	100	100	-7~22	14.0	3~5.2	100	100	2.90	0.16	39
FCA150AC120	1200	150	90	-7~22	9.3	3~5.2	150	90	2.90	0.11	39
FCA300AD170	1700	300	90	-7~22	5.8	3~5.2	300	90	2.90	0.07	40

Connections



OUTLINE DRAWINGS POWER MODULES

fig. 1

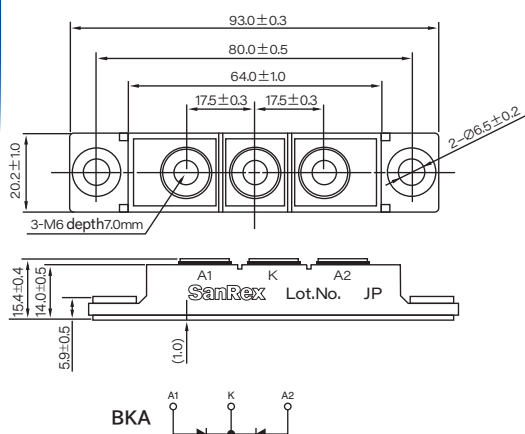


fig. 2

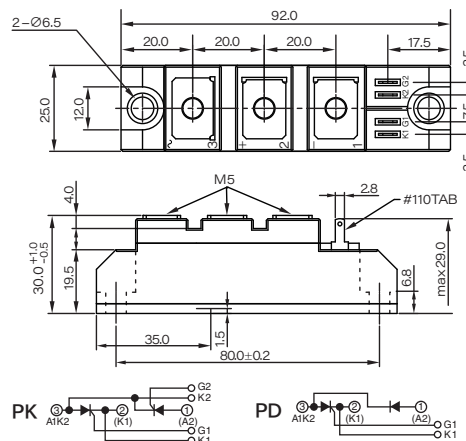


fig. 3

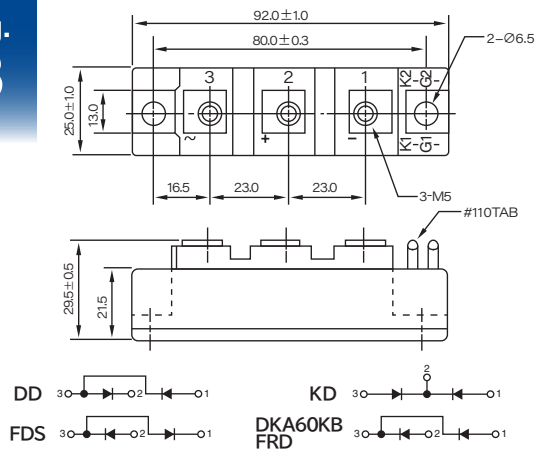


fig. 4

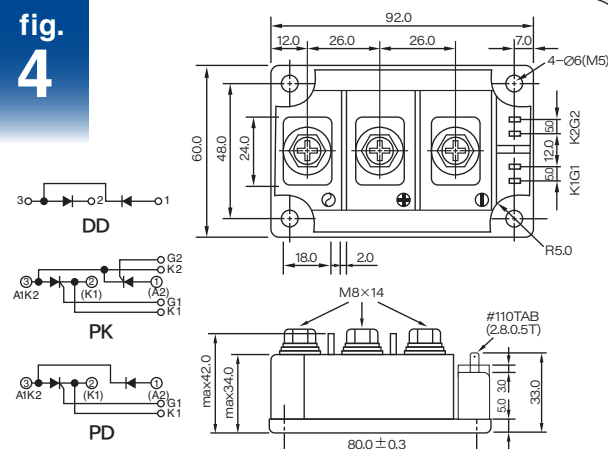


fig. 5

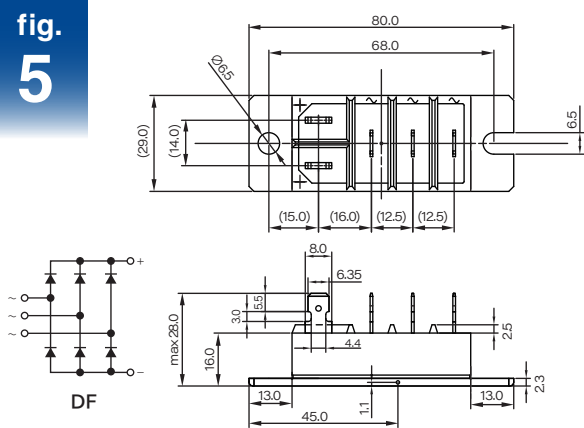


fig. 6

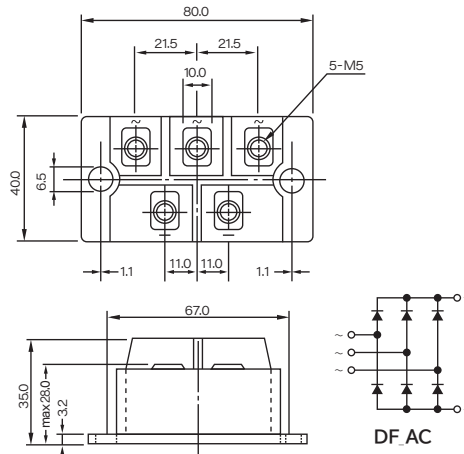


fig. 7

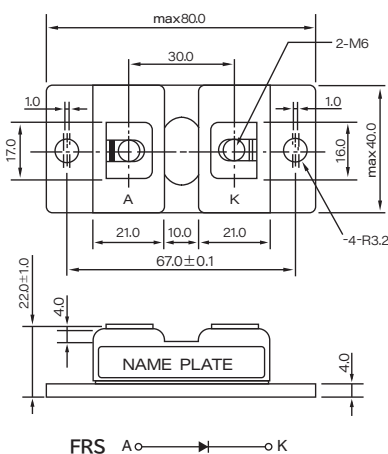


fig. 8

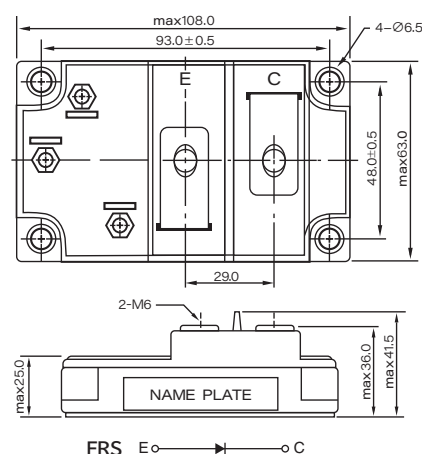




fig. 9

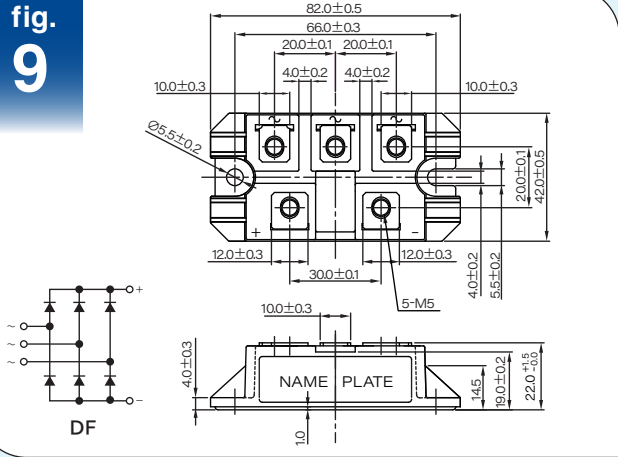


fig. 10

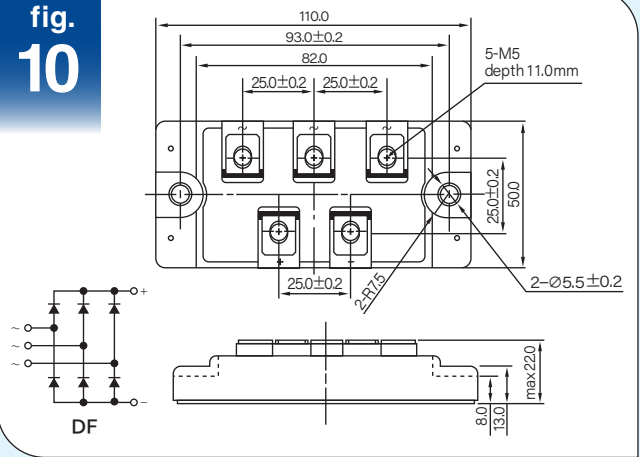


fig. 11

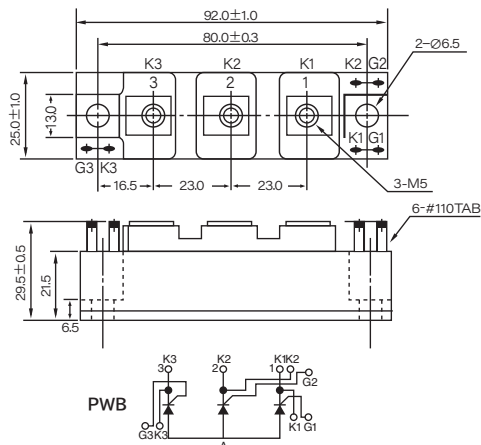


fig. 12

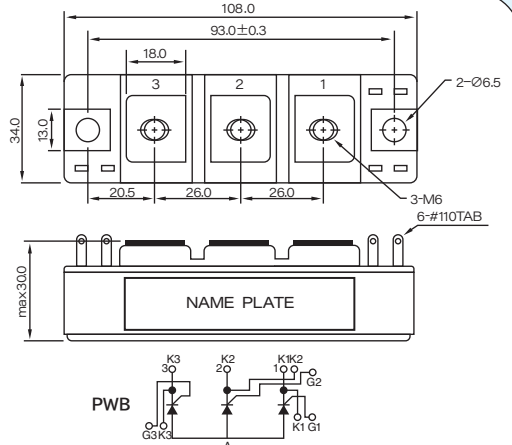


fig. 13

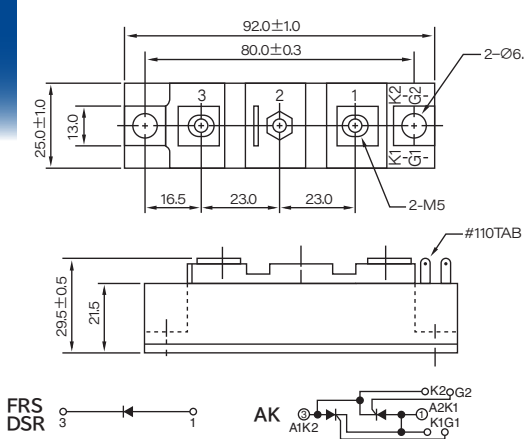


fig. 14

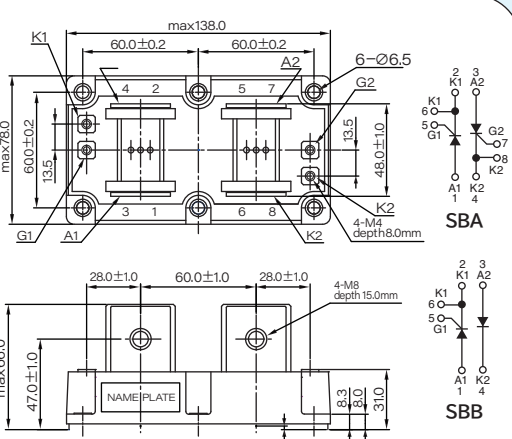


fig. 15

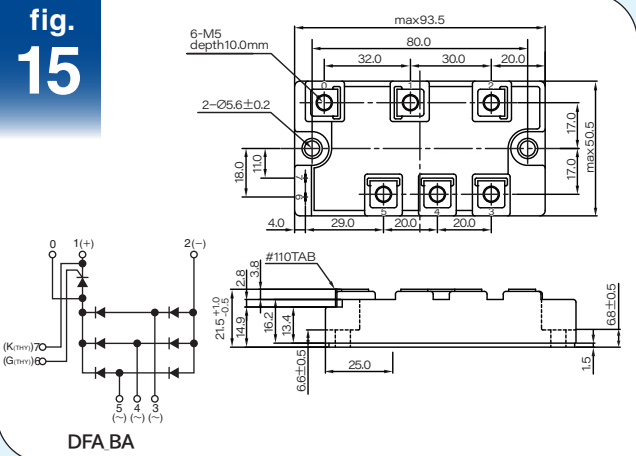


fig. 16

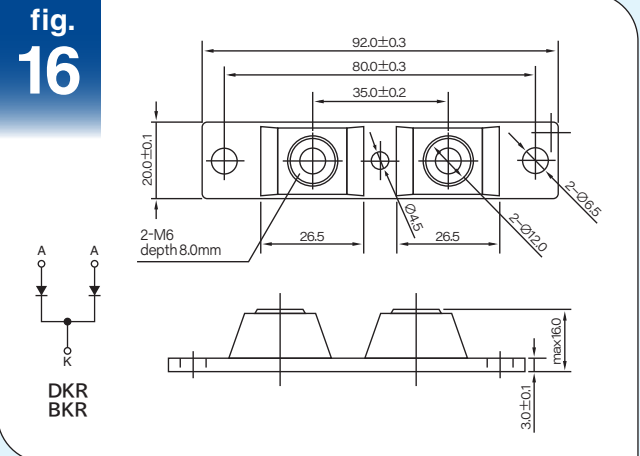




fig.
17

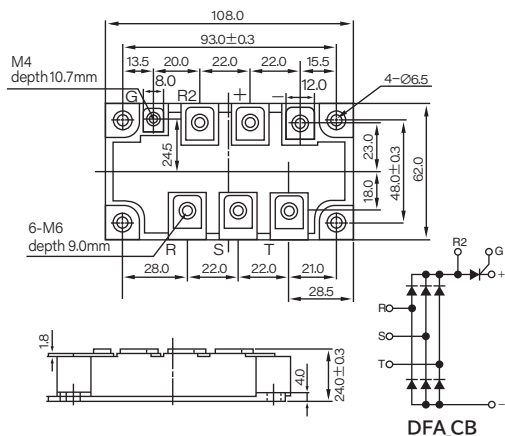


fig.
19

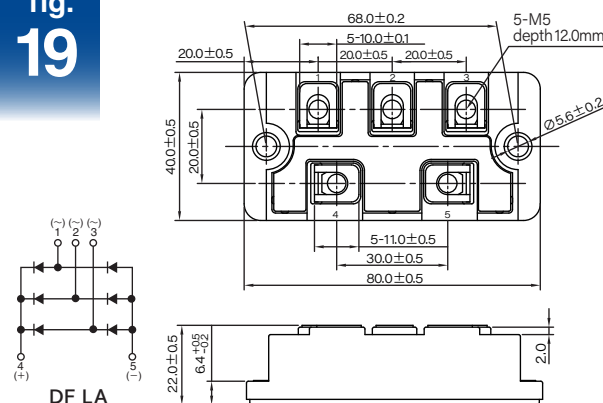


fig.
20

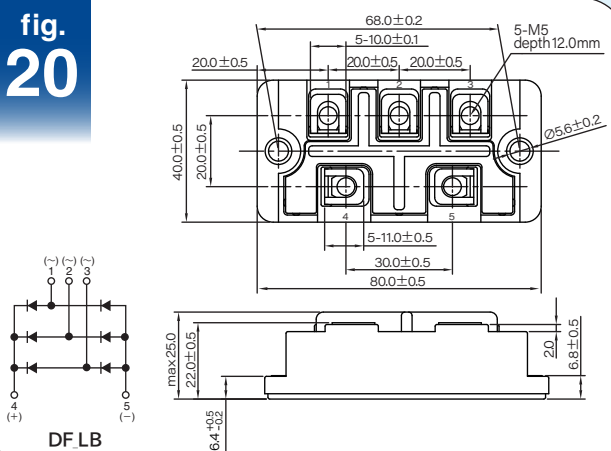


fig.
21

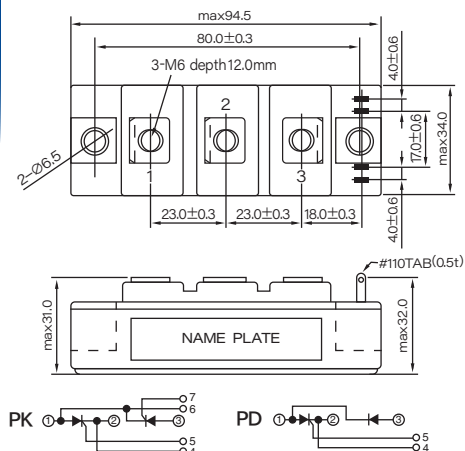


fig.
22

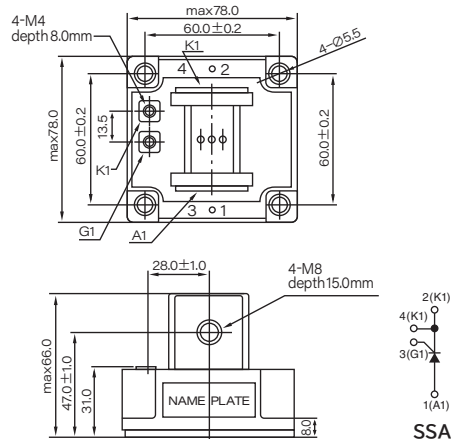


fig.
23

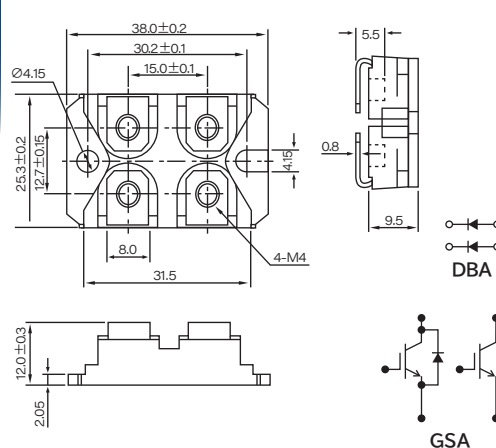


fig.
24

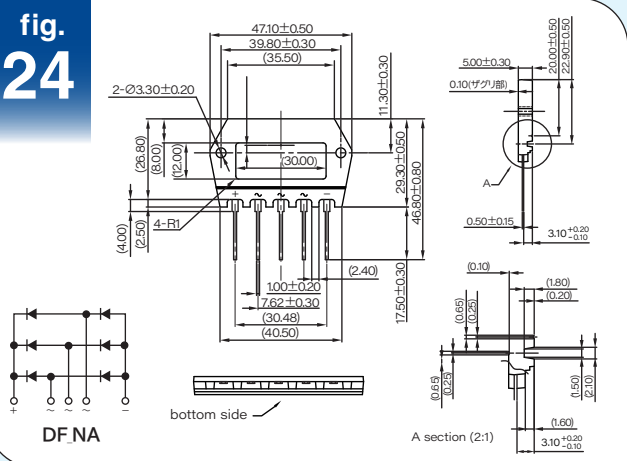
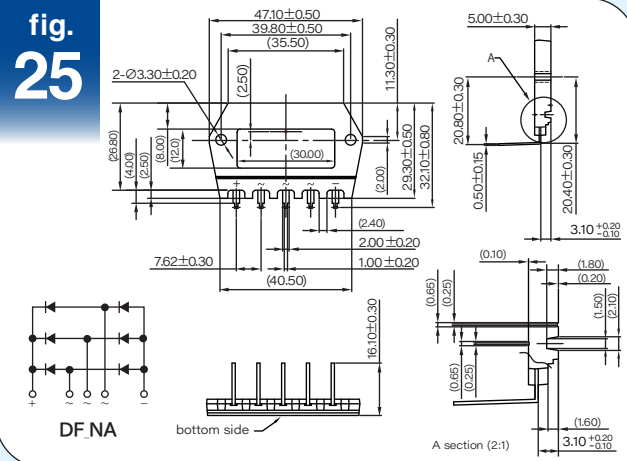


fig.
25



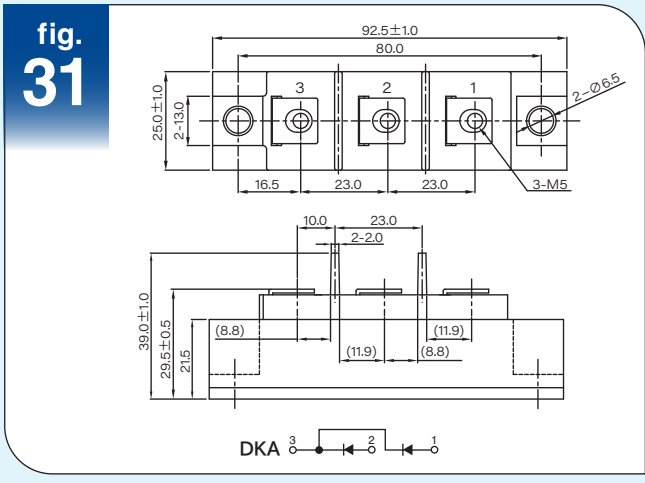
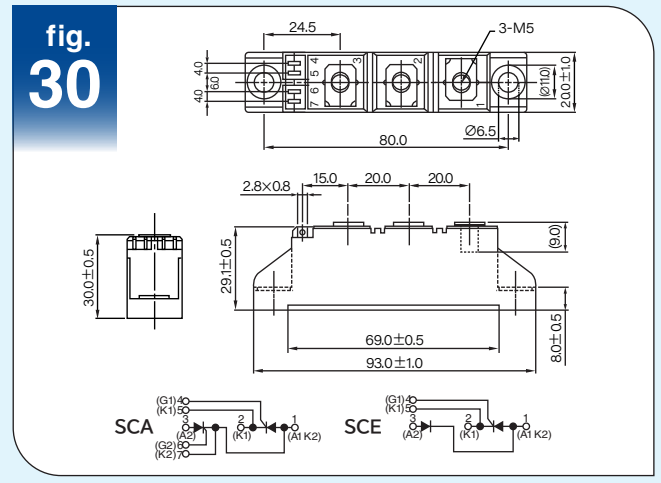
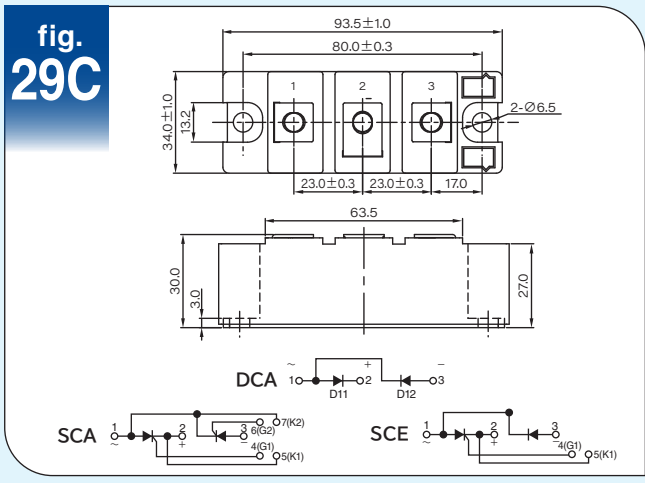
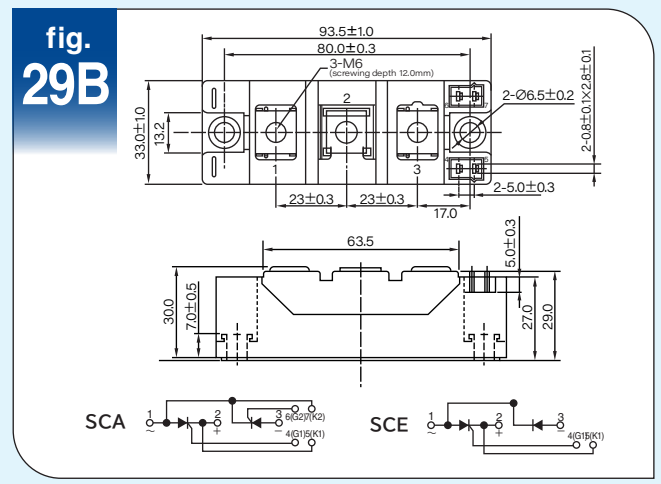
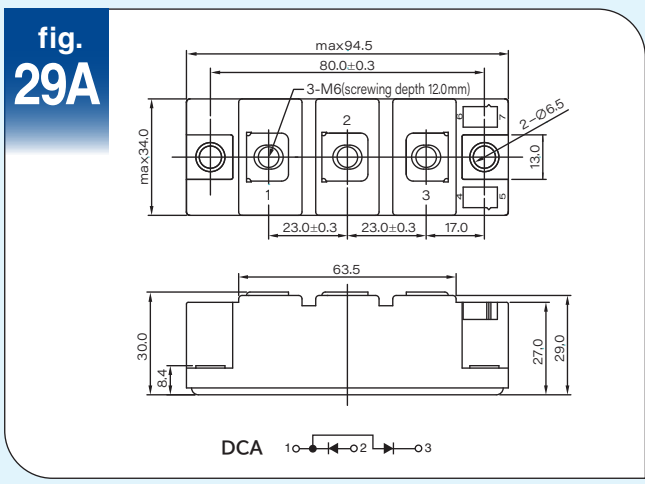
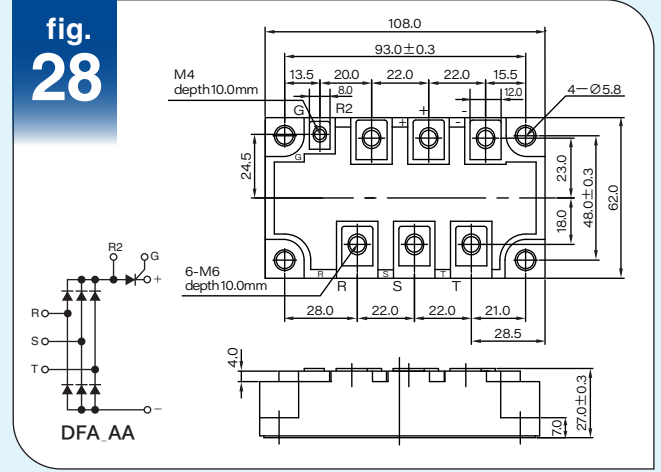
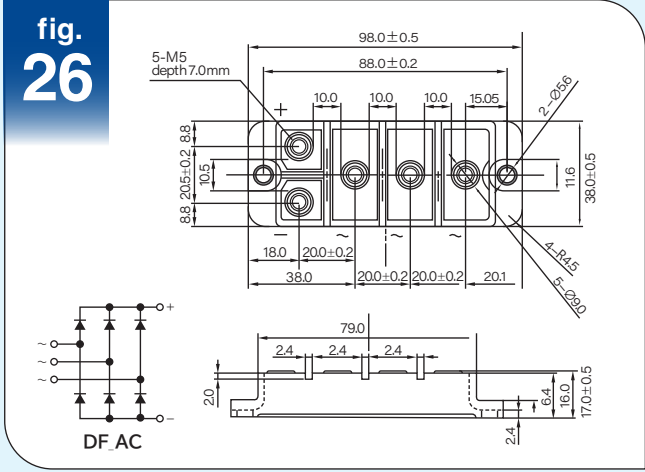




fig.
34A

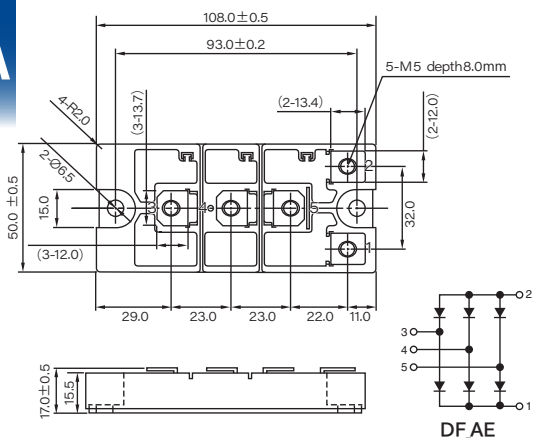


fig.
34B

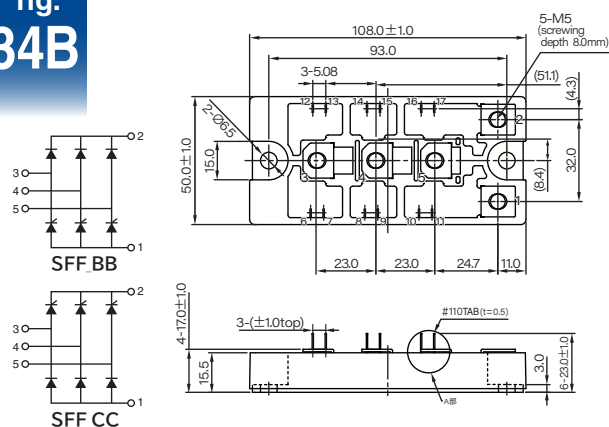


fig.
35

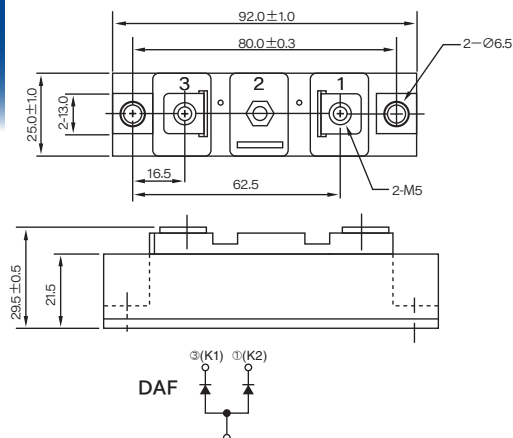


fig.
36

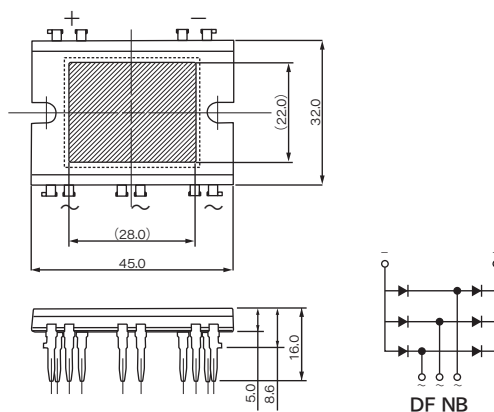


fig.
37

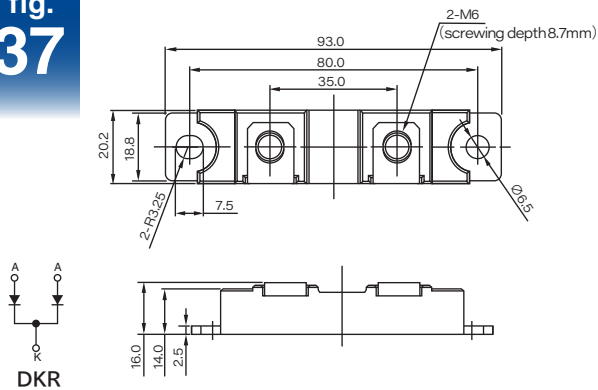


fig.
38

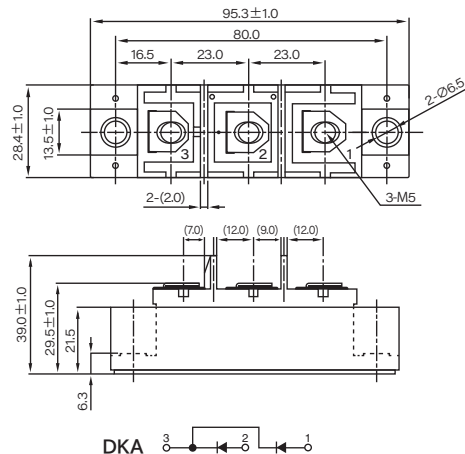


fig.
39

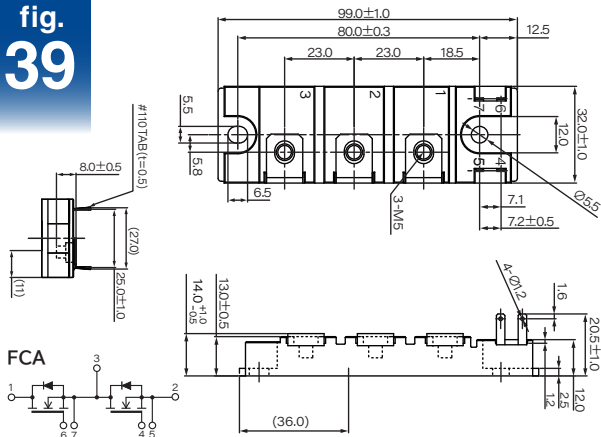
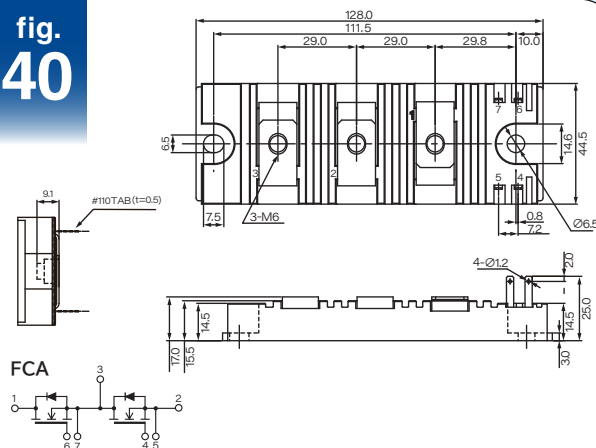
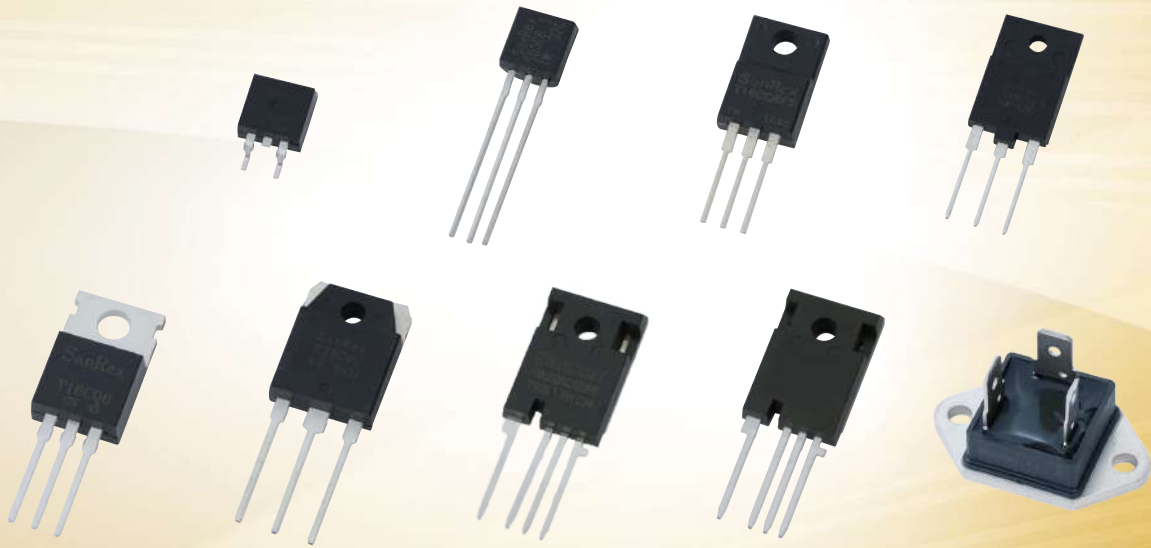


fig.
40





PRODUCT FEATURE

- Triacs **TMG TG** series
- Thyristors **SMG SG** series
- Diodes **DMG DG FRG** series
- SiC MOSFET **FMG** series

Wide variety of products

Through Hole type : 9 models

TO-92, TO-251, TO-220AB, TO-220AB-2L,
TO-220F, TO-3P, TO-3PF, TO-247, TO-247-4L

Surface Mount type : 3 models

SOT-89, TO-252, TO-263

Tab terminal package : 1 model

TO-3

(mA)

Triacs	Standard Gate		Sensitive Gate	
	I ⁺ , I ⁻ , III ⁻	III ⁺	I ⁺ , I ⁻ , III ⁻	III ⁺
TMG1C_			5	10
TMG2C_	15	—		
TMG2D_			5	10
TMG3C_	15	—		
TMG3D_			5	10
TMG5C_	20	—		
TMG8/12/16/20/25C_	30	—		
TMG8/12/16/20/25D_			10	—
TMG40C_	50	—		

Triacs/Thyristors

-Including High sensitivity models

RoHS Compliance

All products shown in catalog are RoHS compliant.

Low loss (VT=1.4V) models available

Triac - Q series

: Guaranteed Tjmax=150°C

Total cost can be reduced by eliminating or reducing size of heat sink.

SiC MOSFET

Isolated TO-247 package with excellent heat dissipation.

UL Standard Compliant

All products shown in catalogue are UL1557 Standard Compliant

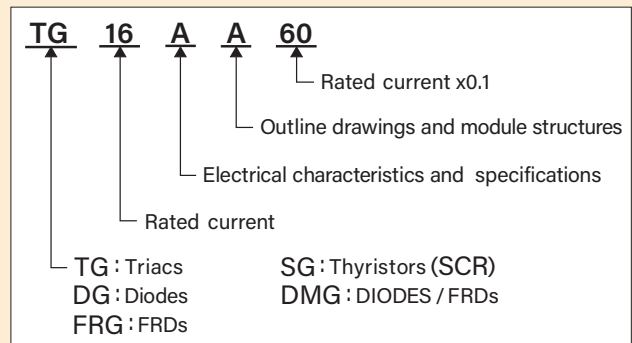
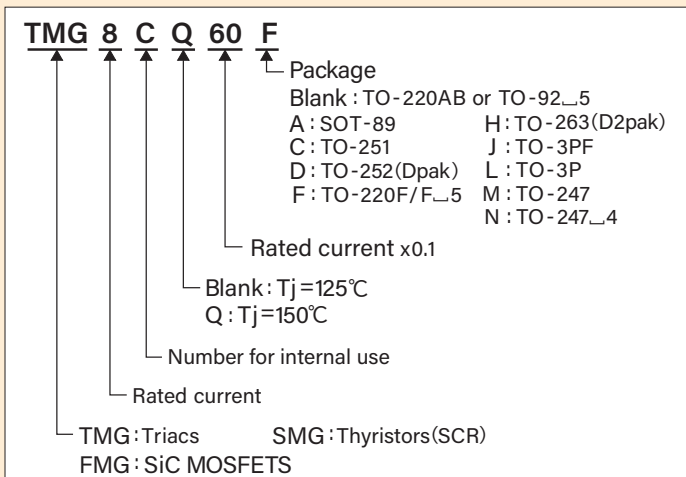
(UL File No.E760102) except for the modules with "Non Isolated Type"

(mA)

Thyristors	Standard Gate	Sensitive Gate
SMG04/05/08C_		0.1
SMG3D_		0.2
SMG5/8C_	10	
SMG12/16C_	30	
SMG5F_		0.2

Can be directly connected with Logic Circuit output.

TYPE DESIGNATION



※ Triacs : RMS On-State Current $I_{T(RMS)}$
Thyristors : Average On-State Current $I_{T(AV)}$
Diodes : Average Forward Current $I_{F(AV)}$
MOSFET : Continuous Drain-Source Current I_D



TRIACS

Through Hole/Standard Gate

Package	Type	V _{DRM} V	I _{T(RMS)} A	I _{DRM} mA	V _{TM} V	I _{GT} mA		V _{GT} V		T _J °C	[dv/dt]c		R _{thj-c} °C/W	Fig No.
						I ⁺ , I ⁻ , III ⁻	III ⁺	I ⁺ , I ⁻ , III ⁻	III ⁺		V/μs (T _J =125°C)	-A/ms [-di/dt]c		
TO-251	TMG3C60/80C*	600, 800	3	1	1.4	15	—	1.5	—	125	5	1.5	3.8	D2
TO-92 5	TMG1D60 5	600	1	0.5	1.75	20	—	1.5	—	125	4	0.5	50	D1
TO-220AB	TMG5C60*	600	5	1	1.4	20	—	1.5	—	125	5	2.5	3	D3
	TMG8C60*	600	8	2	1.4	30	—	1.5	—	125	10	4	2	
	TMG12C60*	600	12	2	1.4	30	—	1.5	—	125	10	6	1.8	
	TMG16C60*	600	16	2	1.4	30	—	1.5	—	125	10	8	1.4	
	TMG20C60*	600	20	2	1.4	30	—	1.5	—	125	10	8	1	D5
TO-220F 5	TMG2C80F5	800	2	1	1.6	15	—	1.5	—	125	3	1	7.5	*D6B
	TMG3C80F5	800	3	1	1.4	15	—	1.5	—	125	5	1.5	5	
	TMG5C80F5	800	5	1	1.4	20	—	1.5	—	125	5	2.5	4	
	TMG8C80F5	800	8	2	1.4	30	—	1.5	—	125	10	4	3.7	
	TMG10C80F5	800	10	2	1.4	30	—	1.5	—	125	10	5	3.5	
	TMG12C80F5	800	12	2	1.4	30	—	1.5	—	125	10	6	3.3	
	TMG16C80F5	800	16	2	1.4	30	—	1.5	—	125	10	8	3	
	TMG20C80F5	800	20	2	1.4	30	—	1.5	—	125	10	8	2.5	
TO-220F	TMG25C60/80F	600, 800	25	5	1.4	30	—	1.5	—	125	10	12.5	1.9	*D6C
TO-3P	TMG25C60/80L*	600, 800	25	5	1.4	30	—	1.5	—	125	10	12.5	1.2	D7
	TMG40C60/80L*	600, 800	40	5	1.4	50	—	1.5	—	125	10	20	0.6	
TO-3PF	TMG25C60/80J	600, 800	25	5	1.4	30	—	1.5	—	125	10	12.5	1.4	*D8
	TMG40C60/80J	600, 800	40	5	1.4	50	—	1.5	—	125	10	20	1.1	

*Non isolated type

*UL File No.E76102

Through Hole / Sensitive Gate

Package	Type	V _{DRM} V	I _{T(RMS)} A	I _{DRM} mA	V _{TM} V	I _{GT} mA		V _{GT} V		T _J °C	[dv/dt]c		R _{thj-c} °C/W	Fig No.
						I ⁺ , I ⁻ , III ⁻	III ⁺	I ⁺ , I ⁻ , III ⁻	III ⁺		V/μs (T _J =125°C)	-A/ms [-di/dt]c		
TO-92 5	TMG1C60/80 5	600, 800	1	0.5	1.6	5	10	1.8	2	125	2	0.5	50	D1
TO-251	TMG3D60/80C*	600, 800	3	1	1.4	5	10	1.5	2	125	5	1.5	3.8	D2
TO-220F 5	TMG2D60F5	600	2	1	1.6	5	10	1.5	2	125	3	1	7.5	*D6B
	TMG2DQ60F5	600	2	1	1.6	5	—	1.5	—	150	1	1	7.5	
	TMG3D60F5	600	3	1	1.4	5	10	1.5	2	125	5	1.5	5	
	TMG5D60F5	600	5	1	1.4	10	—	1.5	—	125	5	2.5	4	
	TMG8D60F5	600	8	2	1.4	10	—	1.5	—	125	10	4	3.7	
	TMG10D60F5	600	10	2	1.4	10	—	1.5	—	125	10	5	3.5	
	TMG12D60F5	600	12	2	1.4	10	—	1.5	—	125	10	6	3.3	
	TMG16D60F5	600	16	2	1.4	10	—	1.5	—	125	10	8	3	
	TMG20D60F5	600	20	2	1.4	10	—	1.5	—	125	10	8	2.5	

*Non isolated type

*UL File No.E76102 **Rth(j-a)

Through Hole / T_J=150°C

Package	Type	V _{DRM} V	I _{T(RMS)} A	I _{DRM} mA	V _{TM} V	I _{GT} mA		V _{GT} V		T _J °C	[dv/dt]c		R _{thj-c} °C/W	Fig No.
						I ⁺ , I ⁻ , III ⁻	III ⁺	I ⁺ , I ⁻ , III ⁻	III ⁺		V/μs (T _J =125°C)	-A/ms [-di/dt]c		
TO-220AB	TMG16CQ60*	600	16	3	1.4	30	—	1.5	—	150	5	8	1.4	D3
	TMG20CQ60*	600	20	3	1.4	30	—	1.5	—	150	5	8	1	D5
TO-220F 5	TMG2CQ60F5	600	2	1	1.6	15	—	1.5	—	150	1	1	7.5	*D6B
	TMG3CQ60F5	600	3	2	1.4	15	—	1.5	—	150	1	1.5	5	
	TMG5CQ60F5	600	5	2	1.4	20	—	1.5	—	150	2	2.5	4	
	TMG8CQ60F5	600	8	2	1.4	30	—	1.5	—	150	5	4	3.7	
	TMG10CQ60F5	600	10	2	1.4	30	—	1.5	—	150	5	5	3.5	
	TMG12CQ60F5	600	12	2	1.4	30	—	1.5	—	150	5	6	3.3	
	TMG16CQ60F5	600	16	3	1.4	30	—	1.5	—	150	5	8	3	
	TMG20CQ60F5	600	20	3	1.4	30	—	1.5	—	150	5	10	2.5	
	TMG2DQ60F5	600	2	1	1.6	5	—	1.5	—	150	1	1	7.5	
	TMG3DQ60F5	600	3	2	1.4	5	10	1.5	2	150	1	1.5	5	
TO-220F	TMG25CQ60F	600	25	5	1.4	30	—	1.5	—	150	5	12.5	1.9	*D6C
TO-3P	TMG25CQ60L*	600	25	5	1.4	30	—	1.5	—	150	5	12.5	1.2	D7
	TMG40CQ60L*	600	40	8	1.4	50	—	1.5	—	150	5	20	0.6	
TO-3PF	TMG25CQ60J	600	25	5	1.4	30	—	1.5	—	150	5	12.5	1.4	*D8
	TMG40CQ60J	600	40	8	1.4	50	—	1.5	—	150	5	20	1.1	

*Non isolated type

*UL File No.E76102

SMD(Surface Mount Device)/Standard Gate

Package	Type	V _{DRM} V	I _{T(RMS)} A	I _{DRM} mA	V _{TM} V	I _{GT} mA		V _{GT} V		T _j °C	[dv/dt]c		R _{thj-c} °C/W	Fig No.
						I ⁺ , I ⁻ , III ⁻	III ⁺	I ⁺ , I ⁻ , III ⁻	III ⁺		V/μs (T _j =125°C)	-A/ms [-di/dt]c		
TO-252 (D pak)	TMG3C60D*	600	3	1	1.4	15	—	1.5	—	125	5	1.5	3.8	D10
	TMG5C60D*	600	5	1	1.4	20	—	1.5	—	125	5	2.5	3	
TO-263 (D2 pak)	TMG16C60H*	600	16	2	1.4	30	—	1.5	—	125	10	8	1.4	D11

* Non isolated type

SMD(Surface Mount Device)/Sensitive Gate

Package	Type	V _{DRM} V	I _{T(RMS)} A	I _{DRM} mA	V _{TM} V	I _{GT} mA		V _{GT} V		T _j °C	[dv/dt]c		R _{thj-c} °C/W	Fig No.
						I ⁺ , I ⁻ , III ⁻	III ⁺	I ⁺ , I ⁻ , III ⁻	III ⁺		V/μs (T _j =125°C)	-A/ms [-di/dt]c		
SOT-89 5	TMG1C60A 5*	600	1	0.5	1.6	5	10	1.8	2	125	2	0.5	**65	D9A
TO-252 (D pak)	TMG3D60D*	600	3	1	1.4	5	10	1.5	2	125	5	1.5	3.8	D10
	TMG5D60D*	600	5	1	1.4	10	—	1.5	—	125	5	2.5	3	

* Non isolated type

**R_{th(j-a)}

SMD(Surface Mount Device)/ T_j=150°C

Package	Type	V _{DRM} V	I _{T(RMS)} A	I _{DRM} mA	V _{TM} V	I _{GT} mA		V _{GT} V		T _j °C	[dv/dt]c		R _{thj-c} °C/W	Fig No.
						I ⁺ , I ⁻ , III ⁻	III ⁺	I ⁺ , I ⁻ , III ⁻	III ⁺		V/μs (T _j =125°C)	-A/ms [-di/dt]c		
TO-252 (D pak)	TMG3CQ60D*	600	3	2	1.4	15	—	1.5	—	150	5	1.5	3.8	D10
	TMG5CQ60D*	600	5	2	1.4	20	—	1.5	—	150	2	2.5	3	

* Non isolated type

*UL File No.E76102

Tab Terminal/Standard Gate

Package	Type	V _{DRM} V	I _{T(RMS)} A	I _{DRM} mA	V _{TM} V	I _{GT} mA		V _{GT} V		T _j °C	[dv/dt]c		R _{thj-c} °C/W	Fig No.
						I ⁺ , I ⁻ , III ⁻	III ⁺	I ⁺ , I ⁻ , III ⁻	III ⁺		V/μs (T _j =125°C)	-A/ms [-di/dt]c		
TO-3	TG16C40/60	400 , 600	16	3	1.5	50	—	3	—	125	6	8	2	*D12
	TG25C40/60	400 , 600	25	5	1.4	50	—	3	—	125	6	15	1.6	
	TG35C60	600	35	5	1.4	50	—	3	—	125	5	15	1.5	
	TG40E60/80	600 , 800	40	5	1.4	50	—	1.5	—	125	6	10	1.3	
not standard	TG70AA40/60	400 , 600	70	10	1.35	50	—	3	—	125	6	8	0.83	D14

*UL File No.E76102

THYRISTORS

Through Hole/Standard Gate

Package	Type	V _{DRM} V	I _{T(AV)} A	I _{T(RMS)} A	I _{DRM} mA	V _{TM} V	I _{GT} mA	V _{GT} V	T _j °C	R _{thj-c} °C/W	Fig No.
TO-220AB	SMG16C60*	600	16	25.1	2	1.5	30	1.4	125	1.4	D3
TO-220F 5	SMG5C60F5	600	5	7.8	2	1.5	10	1.4	125	4	*D6B
	SMG8C60F5	600	8	12.6	2	1.5	10	1.4	125	3.7	
	SMG12C60F5	600	12	18.8	2	1.5	30	1.4	125	3.3	
	SMG16C60F5	600	16	25.1	2	1.5	30	1.4	125	3	
TO-247 NEW NEW	SMG50A160M*	1600	50	79	10	1.86	100	1.5	125	0.25	D16
	SMG80A160M*	1600	80	126	15	1.87	100	1.5	125	0.17	

* Non isolated type

*UL File No.E76102

Through Hole/Sensitive Gate

Package	Type	V _{DRM} V	I _{T(AV)} A	I _{T(RMS)} A	I _{DRM} mA	V _{TM} V	I _{GT} mA	V _{GT} V	T _j °C	R _{thj-c} °C/W	Fig No.
TO-92 5	SMG04C60 5	600	0.4	0.63	0.5	1.2	0.1	0.8	125	**150	D1
	SMG05C60 5	600	0.5	0.78	0.5	1.2	0.1	0.8	125	**150	
TO-251	SMG3D60C*	600	3	4.7	1	1.5	0.2	0.8	125	3.8	D2

* Non isolated type

**R_{th(j-a)}

SMD(Surface Mount Device)/Standard Gate

Package	Type	V _{DRM} V	I _{T(AV)} A	I _{T(RMS)} A	I _{DRM} mA	V _{TM} V	I _{GT} mA	V _{GT} V	T _j °C	R _{thj-c} °C/W	Fig No.
TO-263(D2 pak)	SMG5C60H*	600	5	7.8	2	1.5	10	1.4	125	3	D11

* Non isolated type



SMD(Surface Mount Device)/Sensitive Gate

Package	Type	V _{DRM} V	I _{T(AV)} A	I _{T(RMS)} A	I _{DRM} mA	V _{TM} V	I _{GT} mA	V _{GT} V	T _j °C	Rthj-c °C/W	Fig No.
SOT-89 5	SMG08C60A 5*	600	0.8	1.3	0.5	1.5	0.1	0.8	125	**65	D9A
TO-252 (D pak)	SMG3D60D*	600	3	4.7	1	1.5	0.2	0.8	125	3.8	D10
	SMG5F60D*	600	5	7.8	2	1.8	0.2	0.8	125	3	

*Non isolated type

**Rth(j-a)

Tab Terminal / Standard Gate

Package	Type	V _{DRM} V	I _{T(AV)} A	I _{T(RMS)} A	I _{DRM} mA	V _{TM} V	I _{GT} mA	V _{GT} V	T _j °C	Rthj-c °C/W	Fig No.
TO-3	SG16AA40/60	400, 600	16	25	3	1.5	40	3	125	2	*D12
	SG25AA40/60	400, 600	25	39	5	1.4	40	3	125	1.6	

*UL File No. E76102



FRDs

Through Hole

Package	Type	V _{RRM} V	I _{F(AV)}		I _{FSM} A(60Hz)	I ² t A ² s	V _{FM} V(25°C)	I _{RRM} mA(125°C)	trr ns	Rthj-c °C/W	Fig No.
			A	°C							
TO-3P	DMG60UL20*	200	60	105	900	3375	1.05	2.0(150°C)	60	0.7	D7

*Non isolated type

Tab Terminal

Package	Type	V _{RRM} V	I _{F(AV)}		I _{FSM} A(60Hz)	I ² t A ² s	V _{FM} V(25°C)	I _{RRM} mA(125°C)	trr ns	Rthj-c °C/W	Fig No.
			A	°C							
TO-3	FRG25BA60	600	25	94	450	840	1.3	30(150°C)	100	1.6	*D13
	FRG25CA120	1200	25	78	400	660	1.8	1(150°C)	200	1.6	

*UL File No. E76102



DIODES

Through Hole

Package	Type	V _{RRM} V	I _{F(AV)}	I _{FSM} A(60Hz)	I ² t A ² s	V _{FM} V(25°C)	I _{RRM} mA(125°C)	trr ns	Rthj-c °C/W	Fig No.
TO-220AB-2L	DMG35AA100*	1000	35	300	380	1.2	100	180	1.0	D4

*Non isolated type

Tab Terminal

Package	Type	V _{RRM} V	I _{F(AV)}		I _{FSM} A(60Hz)	I ² t A ² s	V _{FM} V(25°C)	I _{RRM} mA(150°C)	Rthj-c °C/W	Fig No.
			A	°C						
TO-3	DG20AA80/120/160	800,1200,1600	20	101	450	840	1.65	8	1.6	*D13

*UL File No. E76102



SiC MOSFETs

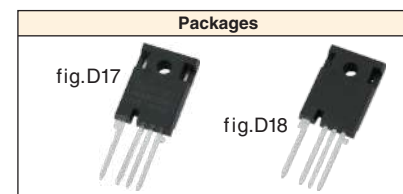
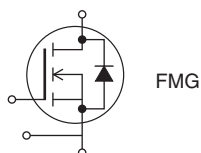
SiC MOSFET FMG Series

V_{iso}: 2500V(RMS) T_{j(max)}: 150°C

Package	Type	MOSFET						チャンネルダイオード			Rthj-c °C/W	Fig No.
		V _{DSS} V	I _D		V _{GSS} V	R _{DS(on)} mΩ	V _{GS(th)} V	I _D		V _{SD} V		
			A	°C				A	°C			
NEW TO-247-4L	FMG50AQ120N6	1200	50	108	-7~22	28.0	3~5.2	50	108	2.90	0.28	*D17
NEW	FMG50AQ170N6	1700	50	101	-7~22	31.0	3~5.2	50	101	2.90	0.28	*D18

*UL File No. E76102

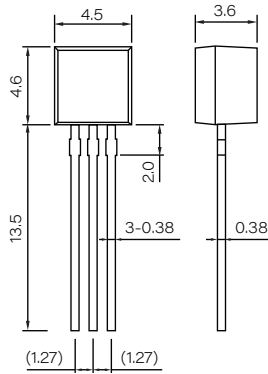
Connections





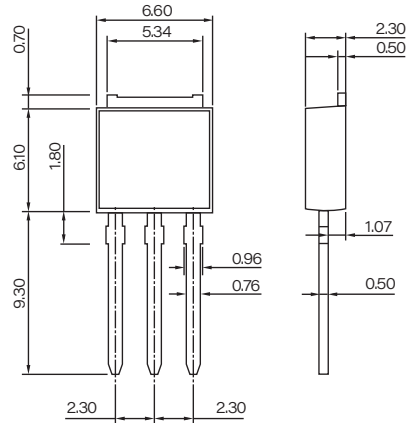
OUTLINE DRAWINGS DISCRETES

fig. D1



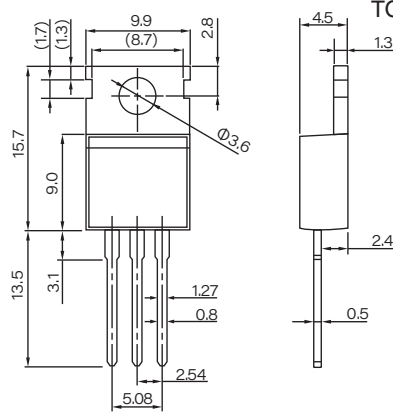
TO-92 5

fig. D2



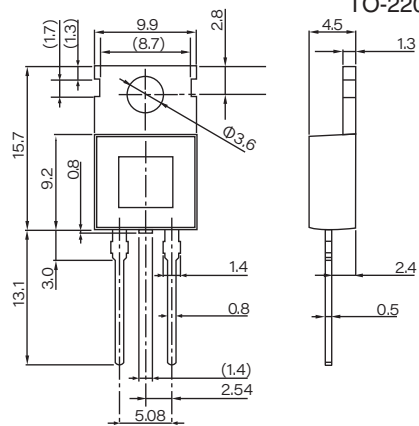
TO-251

fig. D3



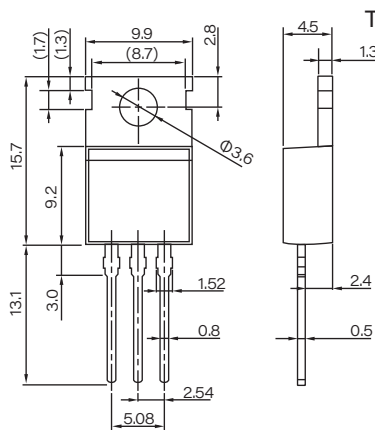
TO-220AB

fig. D4



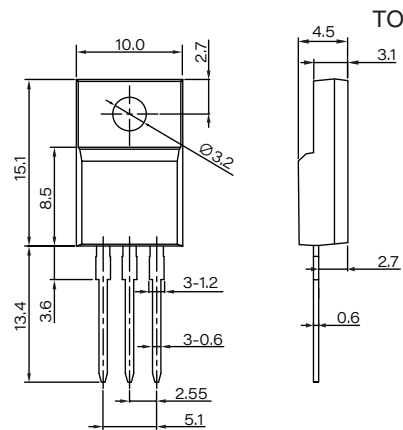
TO-220AB-2L

fig. D5



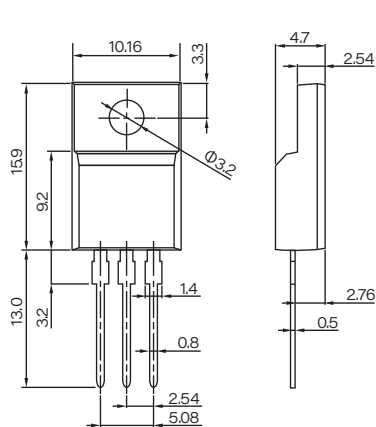
TO-220AB 2

fig. D6B



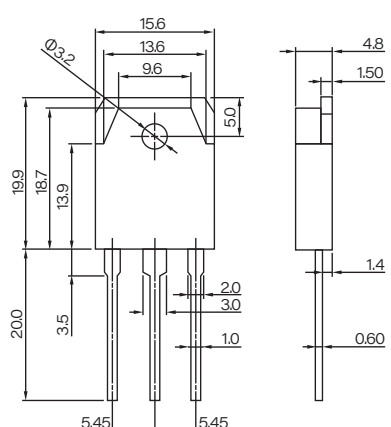
TO-220F 5

fig. D6C

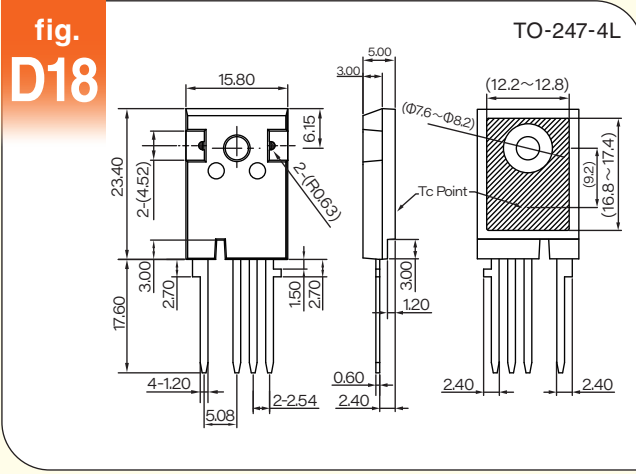
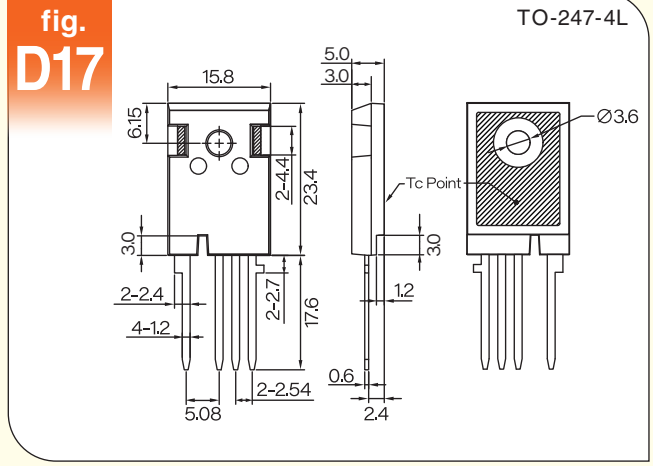
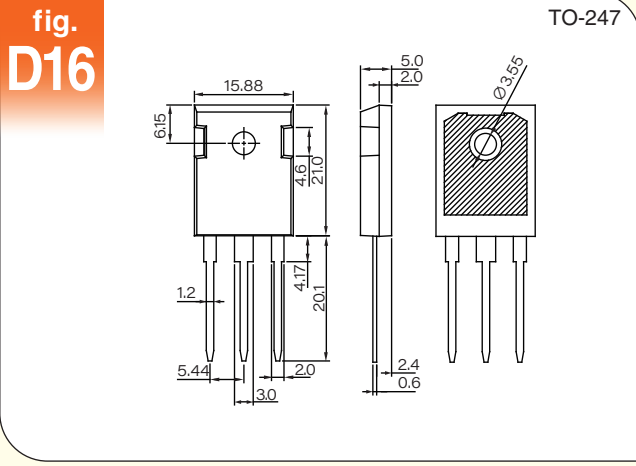


TO-220F 2

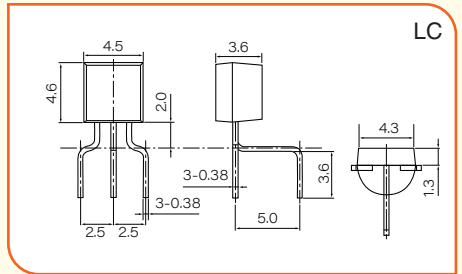
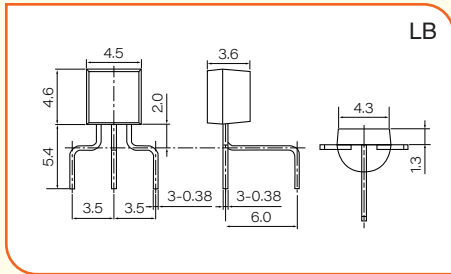
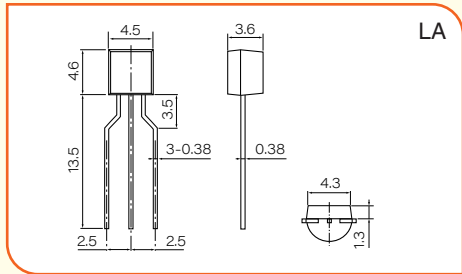
fig. D7



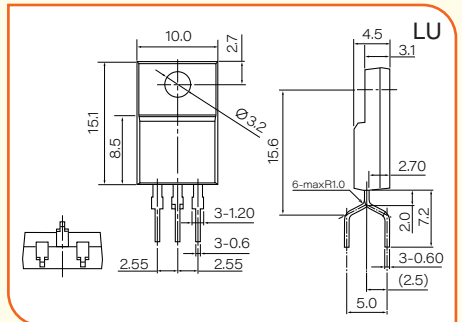
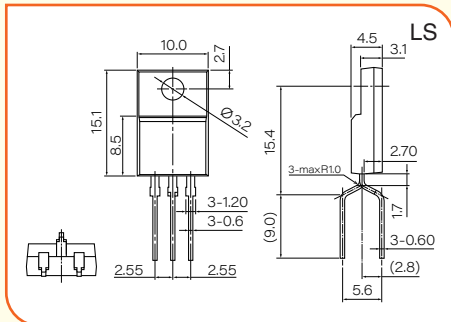
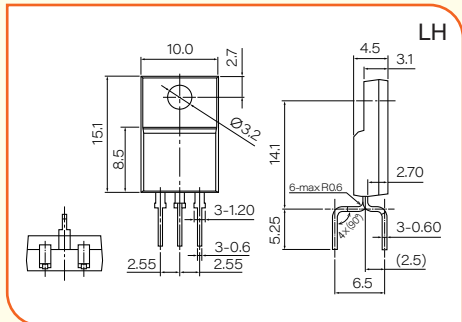
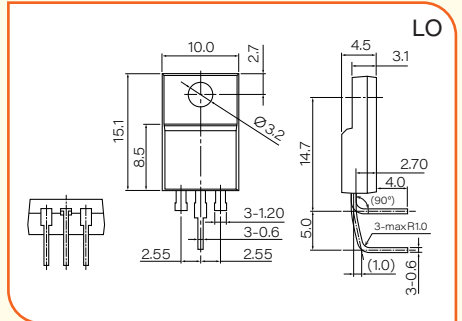
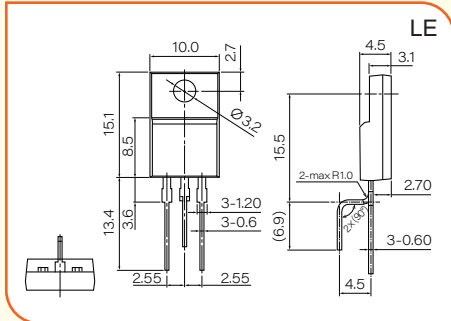
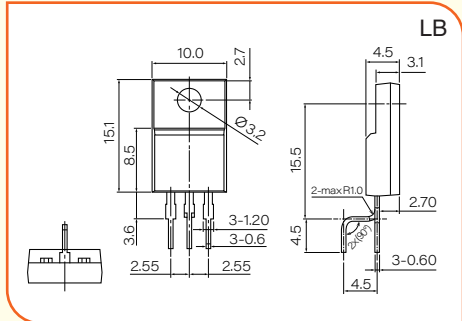
TO-3P



● TO-92 5 LEAD FORMING



● TO-220F 5 LEAD FORMING





PACKAGING SPECIFICATIONS Through Holes

TO-92 5 (Straight Lead)

Bag (Polyethylene)
1,000 pcs per bag

Inner box (Corrugated card board)
6 bags (6,000 pcs) per inner box

Outer box (Corrugated card board)
4 inner boxes (24,000 pcs) per outer box

Note) Type and quantity are indicated on the outer box.

TO-92 5 (Formed Lead)

Bag (Polyethylene)
1,000 pcs per bag

Inner box 1 (Corrugated card board)
1 bag (1,000 pcs) per inner box 1

Inner box 2 (Corrugated card board)
6 inner box 1 (6,000 pcs) per inner box 2

Outer box (Corrugated card board)
4 inner box 2 (24,000 pcs) per outer box

Note) Type and quantity are indicated on the outer box.

TO-92 5 (Taping)

P0: Accumulative pitch error $\pm 1.0/20$ pitch

Inner box 2,000 pcs per box (Corrugated card board)

Outer box 5 packing boxes (10,000 pcs) per box (Corrugated card board)

Note) Type and quantity are indicated on the outer box.

TO-251

Tube (PVC plastic) 70 pcs per tube

Inner box (Corrugated card board)
72 tubes (5,040 pcs) per inner box

Outer box (Corrugated card board)
6 inner boxes (30,240 pcs) per outer box

6 rows 12 levels

Note) Type and quantity are indicated on the outer box.

TO-220AB/TO-220AB 2/TO-220AB-2L

Tube (PVC plastic) 50 pcs per tube

Inner box (Corrugated card board)
20 tubes (1,000 pcs) per inner box

Outer box (Corrugated card board)
4 inner boxes (4,000 pcs) per outer box

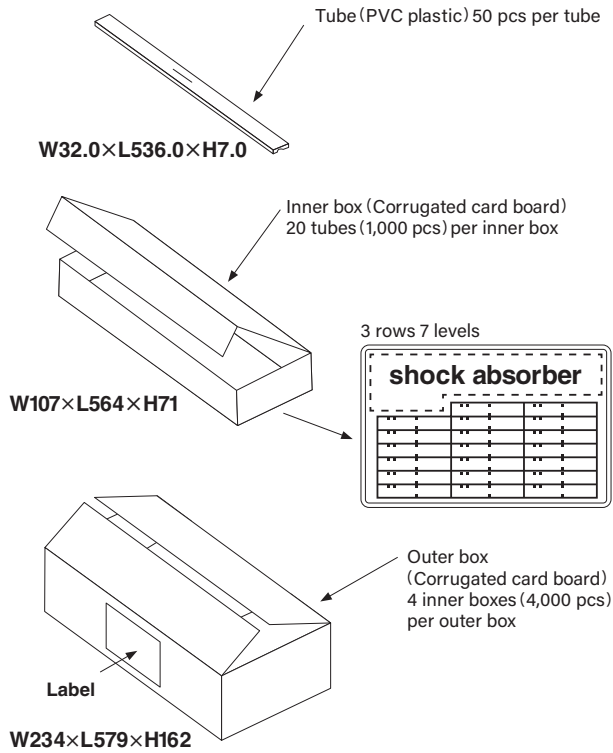
3 rows 7 levels

Cushioning material (Corrugated card board)

Note) Type and quantity are indicated on the outer box.

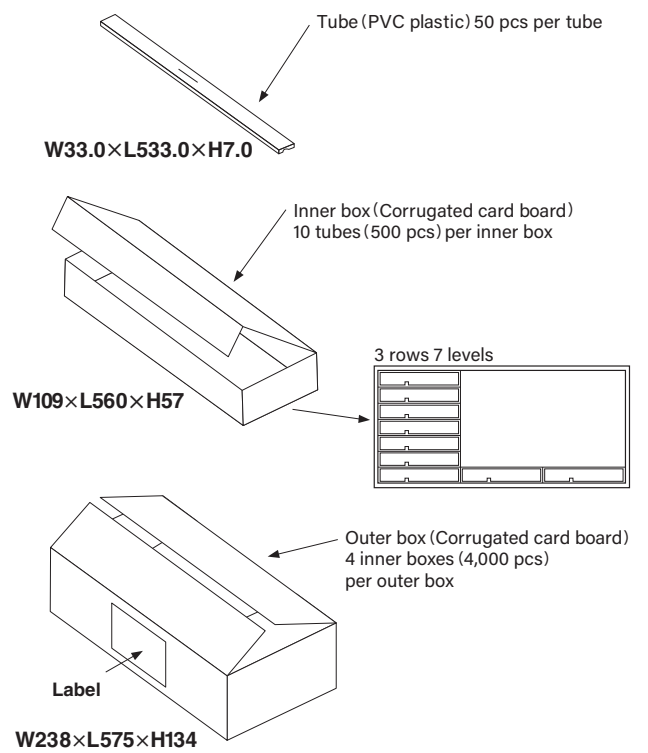


TO-220F 5 (Straight Lead)



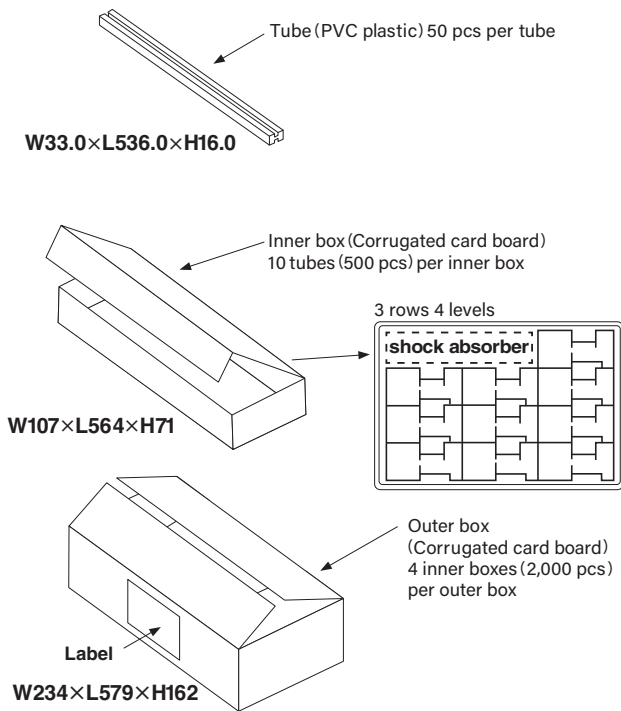
Note) Type and quantity are indicated on the outer box.

TO-220F 2 (Straight Lead)



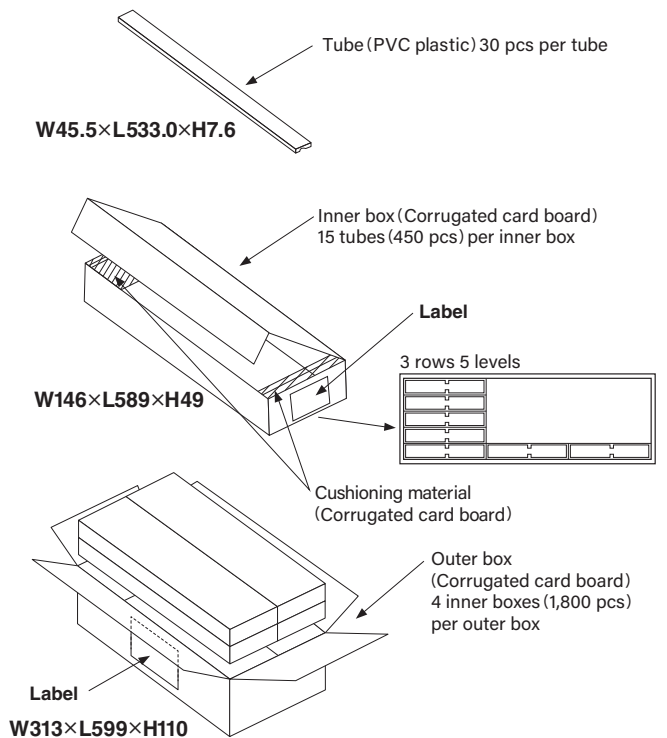
Note) Type and quantity are indicated on the outer box.

TO-220F 5 (Formed Lead)



Note) Type and quantity are indicated on the outer box.

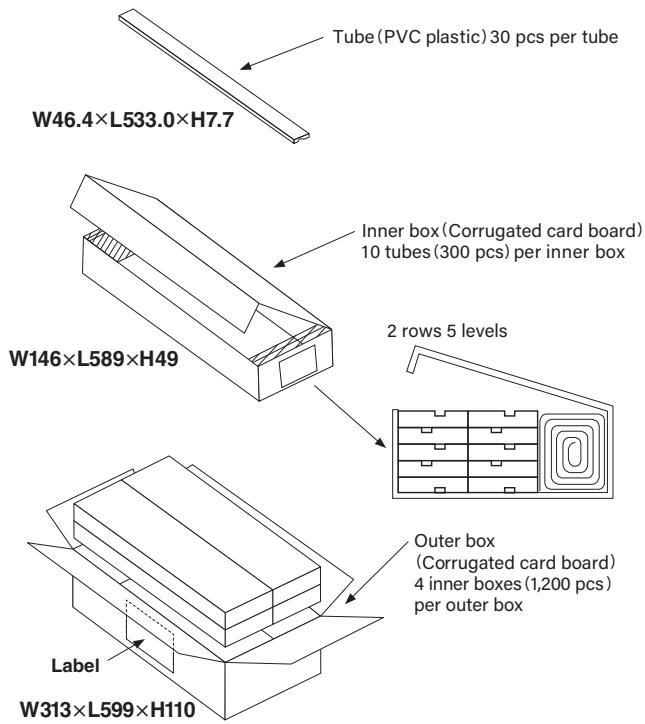
TO-247



Note) Type and quantity are indicated on the outer box.

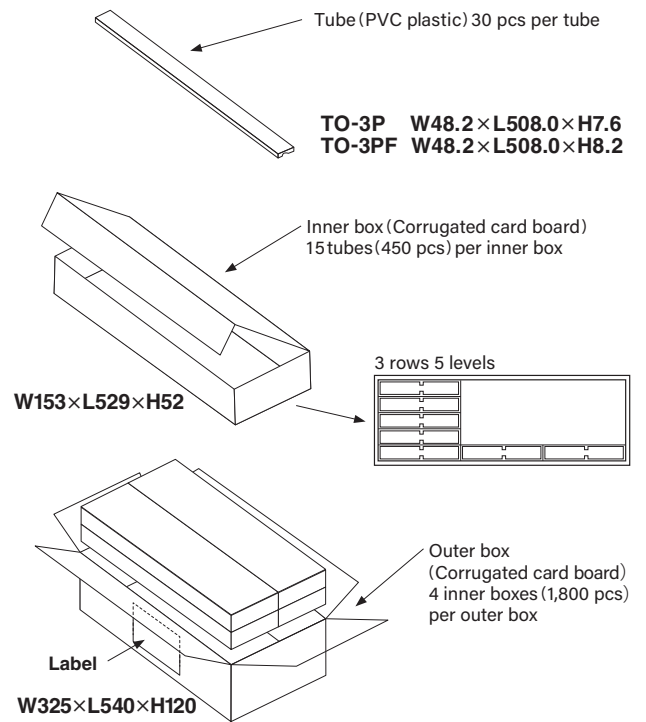


TO-247-4L



Note) Type and quantity are indicated on the outer box.

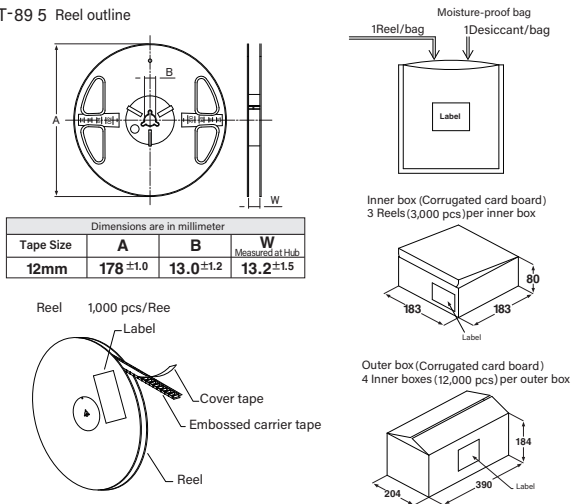
TO-3P/TO-3PF



Note) Type and quantity are indicated on the outer box.

SOT-89 5

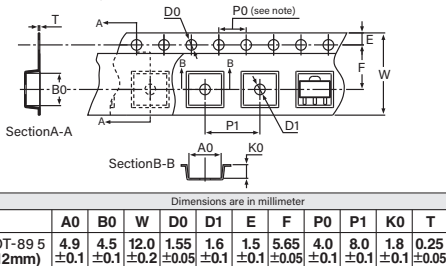
SOT-89 5 Reel outline



Dimensions are in millimeter			
Tape Size	A	B	W
12mm	178 ±1.0	13.0 ±1.2	13.2 ±1.5

Notes Type, lot number and quantity are indicated on the reel, moisture-proof bag, inner box and outer box.

SOT-89 5 Embossed carrier tape outline

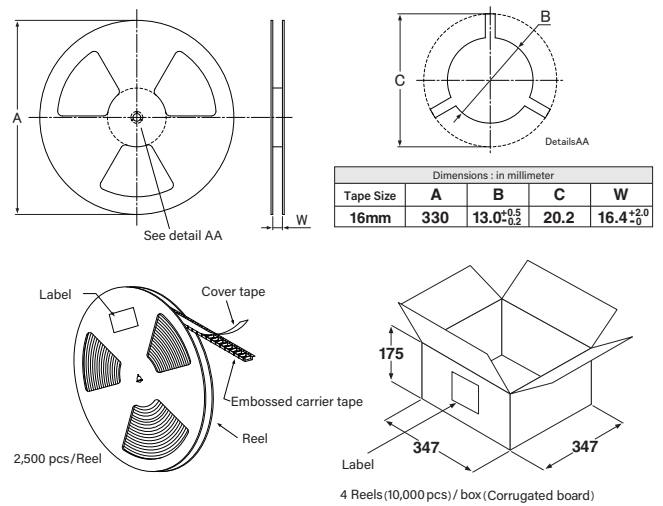


Dimensions are in millimeter											
	A0	B0	W	D0	D1	E	F	P0	P1	K0	T
SOT-89 5 (12mm)	4.9 ±0.1	4.5 ±0.1	12.0 ±0.2	1.55 ±0.05	1.6 ±0.1	1.5 ±0.05	5.65 ±0.1	4.0 ±0.1	8.0 ±0.1	1.8 ±0.1	0.25 ±0.05

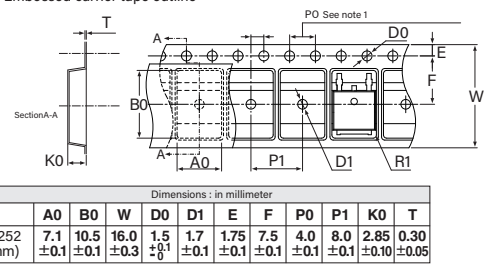
Notes) 10 sprocket hole pitch cumulative tolerance ±0.2

TO-252

TO-252 Reel outline



TO-252 Embossed carrier tape outline



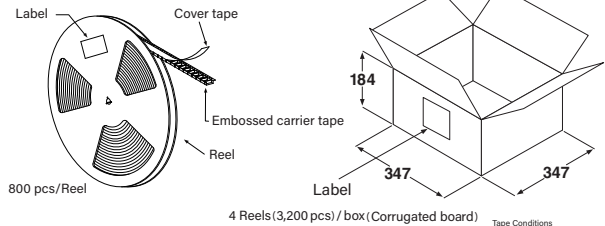
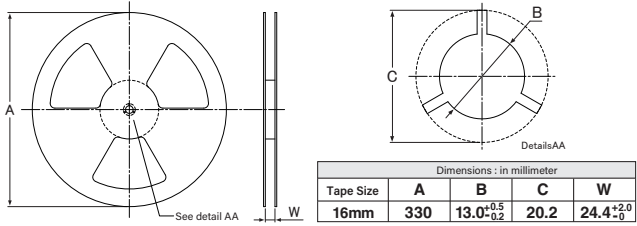
Dimensions : in millimeter											
	A0	B0	W	D0	D1	E	F	P0	P1	K0	T
TO-252 (16mm)	7.1 ±0.1	10.5 ±0.1	16.0 ±0.3	1.5 ±0.1	1.7 ±0.1	1.75 ±0.1	7.5 ±0.1	4.0 ±0.1	8.0 ±0.1	2.85 ±0.1	0.30 ±0.05

Note) 10 sprocket ; Accumulated pitch error : ±0.2

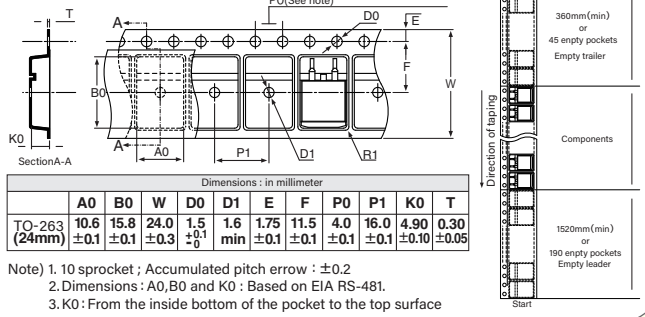


TO-263

TO-263 Reel outline

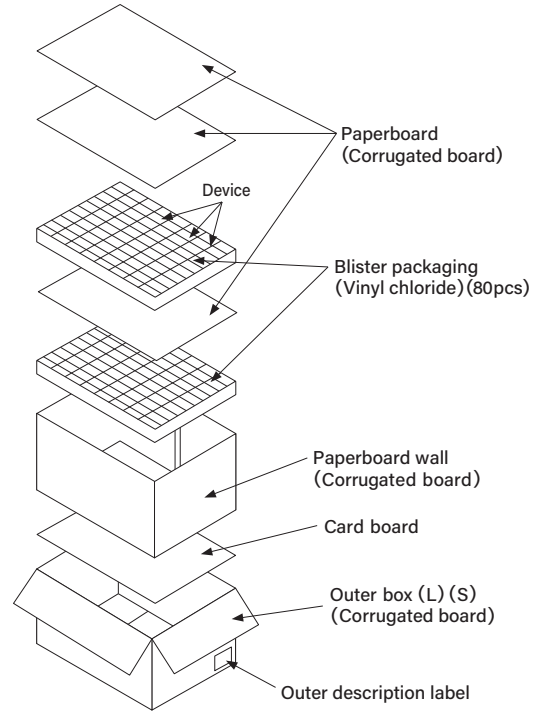


TO-263 Embossed carrier tape outline



Tab Terminal

TO-3



- For Outer carton (L) ; Maximum 5 stacks of partition tray (400 pcs)
W395 × L295 × H185mm
- For Outer carton (S) ; Maximum 2 stacks of partition tray (160 pcs)
W395 × L295 × H105mm

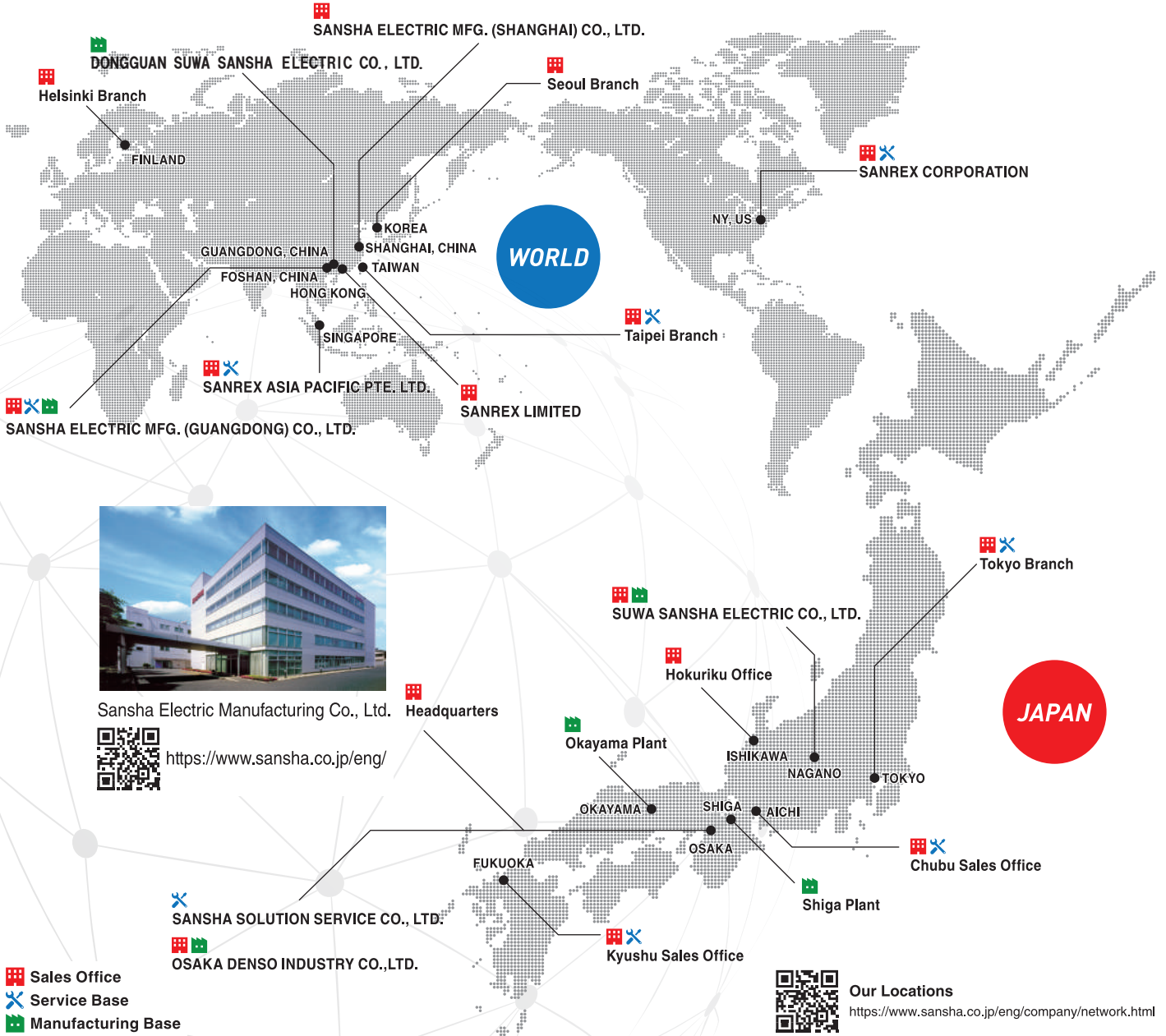
SanRex
SANSHA ELECTRIC MANUFACTURING CO., LTD.



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- c. Use for trunk systems that play important roles socially and publicly
- d. Devices and systems that are similar to any of the above

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